

MPS camera projects

MPS has more than 25 years experience in providing FPAs for space-based solar and planetary scientific missions, and for ground-based solar telescopes.

Selected projects

Planetary:

- Giotto: HMC (1986)
- Mars Pathfinder: IMP (1997)
- Rosetta: OSIRIS cameras (launched 2004)
- Cassini/Huygens: DISR camera (2005)
- Venus Express: VMC (launched 2005)
- Dawn: FC 1 and 2 (launched 2007)
- Phoenix: RAC (2008)

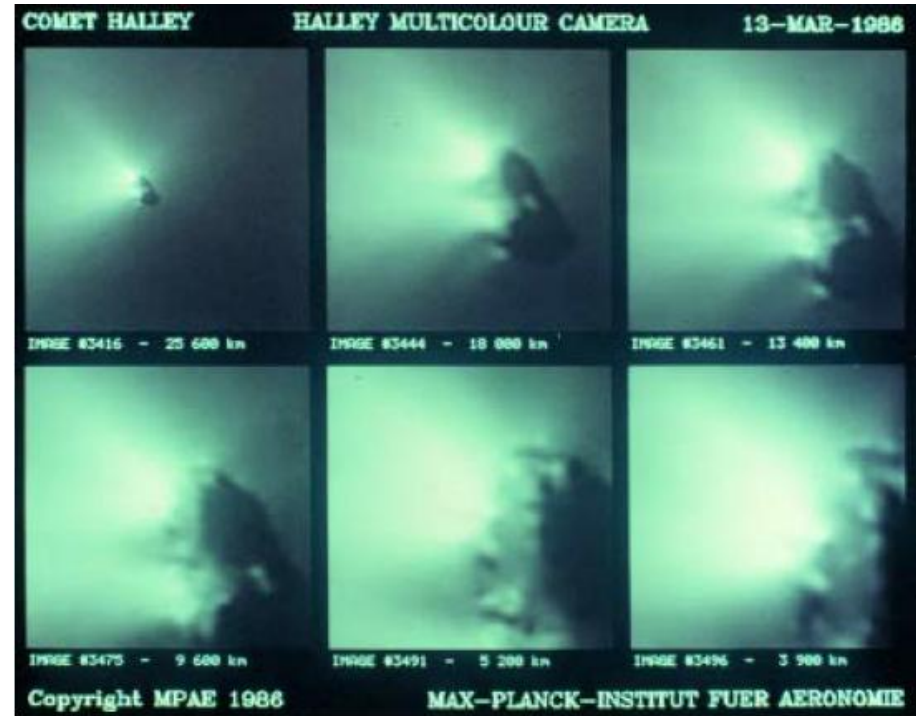
Solar:

- VTT, GREGOR: TIP 2 (ground-based, since 2005)
- Sunrise: SuFI (2009)
- RAISE
- SMESE
- Solar Orbiter EUV Lyman-Alpha camera
- Solar Orbiter: ISPHI
- Solar Orbiter METIS

Giotto - HMC

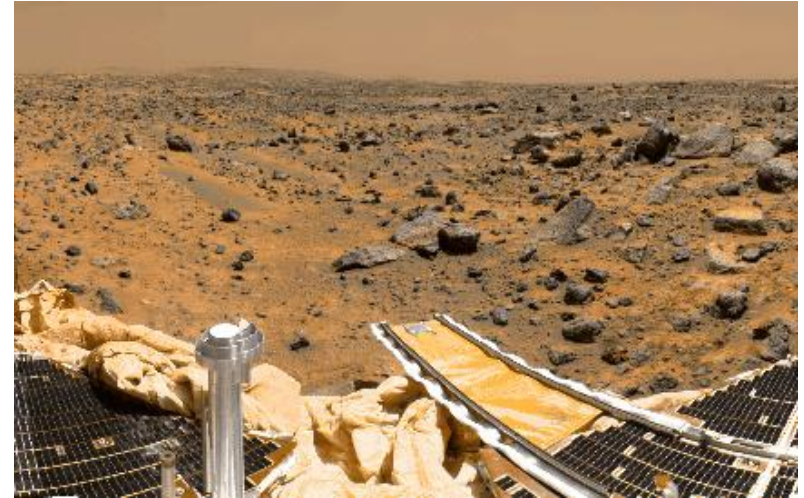
- Comet Halley flyby, 1986

The Halley Multicolour Camera (HMC) has recorded more than 2000 images. The 6 images shown on the right range between 6 min. and 1 min. before closest approach.



Mars Pathfinder - IMP

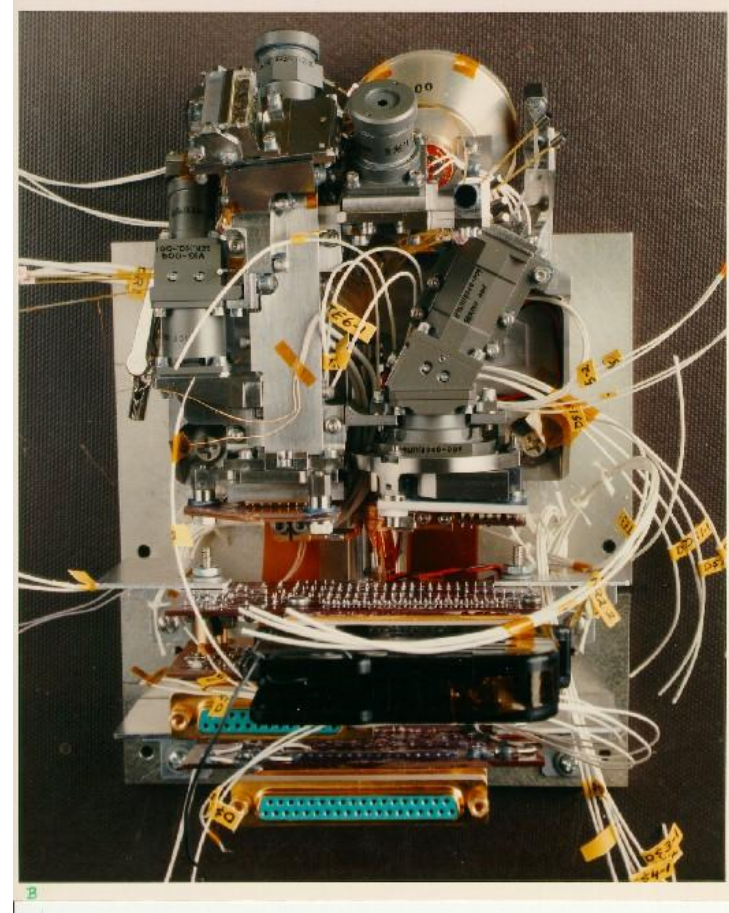
- NASA mission, mars landing 1997
- First successful deployment of a rover on the Martian surface.
- Imager for Mars Pathfinder (IMP) a stereoscopic camera mounted on top of an expandable pole on the lander unit.
- MPS has provided the CCD sensor and the readout board for IMP.



Segment of a panoramic image, recorded by the IMP.

Cassini/Huygens - DISR camera

- NASA/ESA mission, launched 1997 to study Saturn and its moons
- DISR has recorded spectra of the Titan atmosphere during the descent of the Huygens probe (Jan, 2005)
- MPS was responsible for CCD detector and associated electronics
Image compression board developed in collaboration with IDA



View of the open DISR instrument from above, during assembly

Dawn - FC 1 and 2

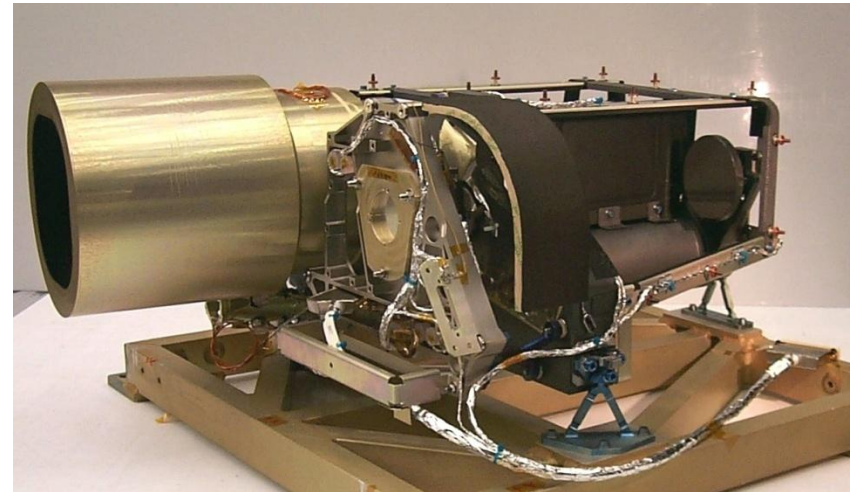
- Mission of the NASA discovery program to study Vesta and Ceres in the asteroid belt
- Has reached Vesta on July 16, 2011 and will arrive at Ceres in Feb 2015
- MPS has built the 2 identical Framing Cameras, with DLR and IDA (Braunschweig).



One of the FCs; 1k x 1k CCD with a huge range of integration times (1ms to 3.5 hours).

Rosetta - OSIRIS

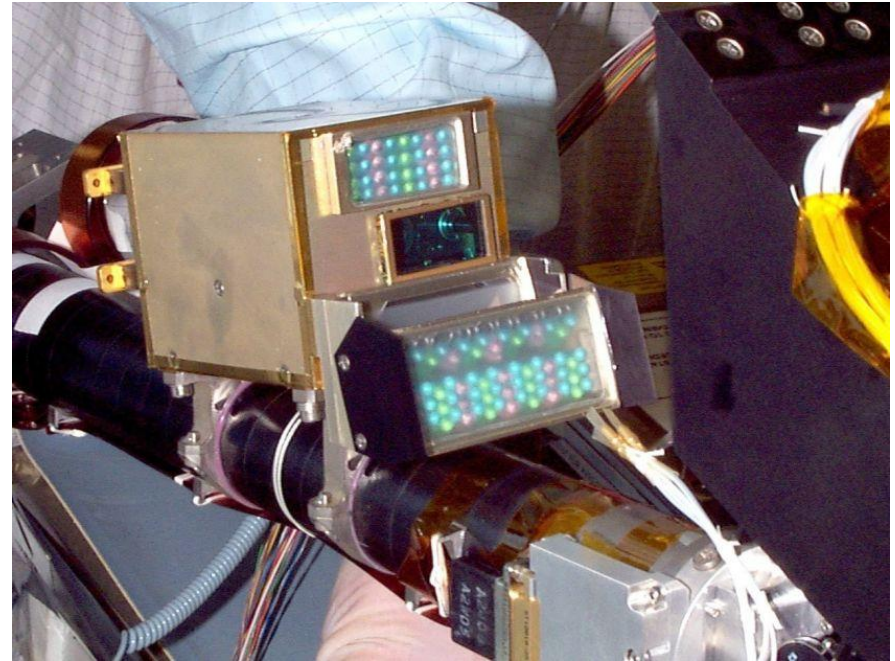
- The two OSIRIS cameras, the main scientific imaging system on the orbiter of ESA's Rosetta mission to comet 67P/Churyumov-Gerasimenko (encounter in 2014)
- FPA units built at MPS



OSIRIS narrow-angle (top) and wide-angle (bottom) cameras

Phoenix - RAC

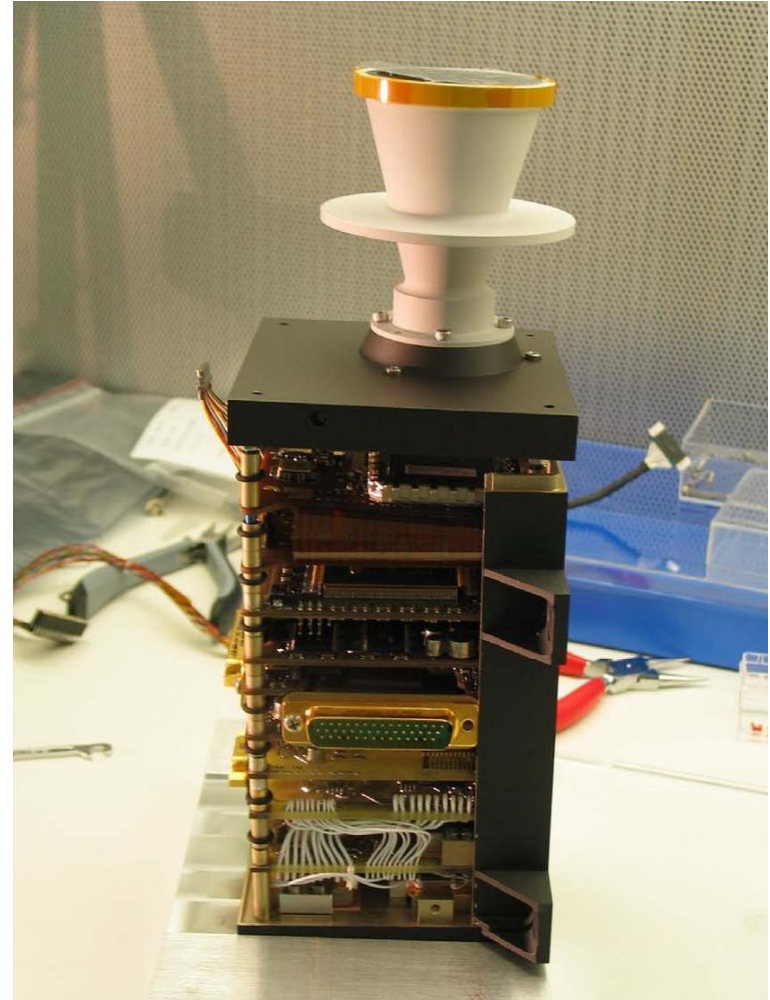
- NASA mission to the Martian arctic region (landed on May 25, 2008)
- MPS has contributed the Robotic Arm Camera (RAC), with the Univ. of Arizona



RAC with colored LEDs and microscope optics allowing the study of Martian soil particles down to 50 μm .

Venus Express - VMC

- ESA's first mission to Venus (launched on Nov 9, 2005)
- Venus monitoring camera (VMC) monitors the dynamics of the Venus atmosphere in 4 different spectral windows between the UV and the near-IR.
- VMC developed by MPS in coll. with IDA and DLR.



VTT, GREGOR - TIP 2

- Based on 1k x 1k, HgCdTe CCD from Teledyne (former Rockwell)
- Used for ground-based near-IR solar spectro-polarimetry

Sunrise - SuFI

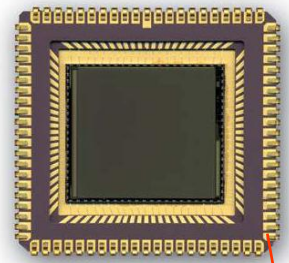
- Adaptation of an off-the-shelf camera (PixelVision) for the Sunrise balloon flight experiment
- Hi-res observations in the 200-400nm range



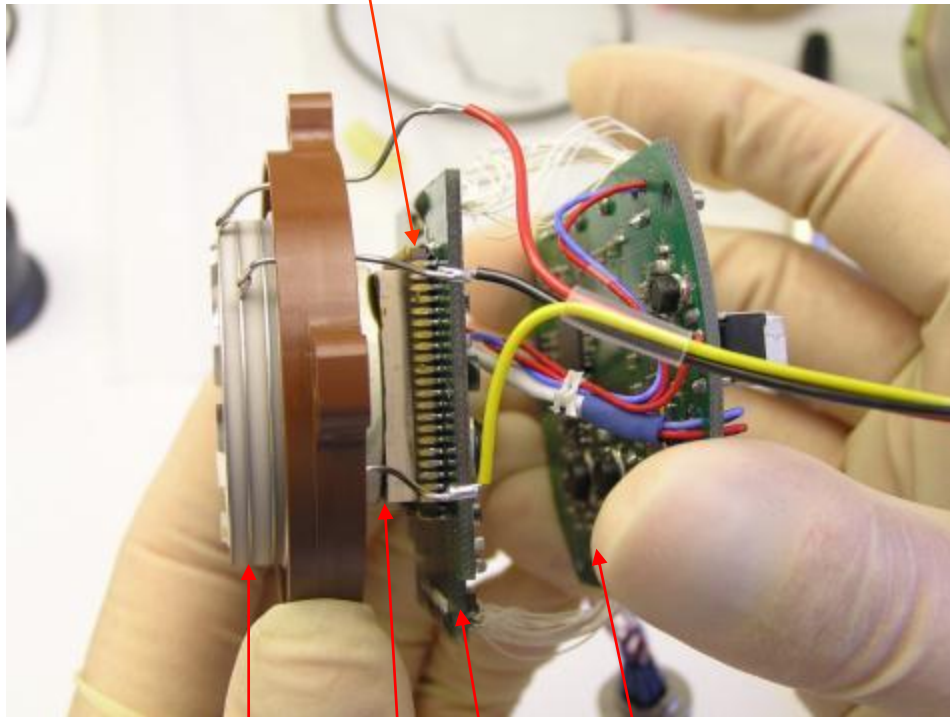
VUV / EUV cameras with MCP intensifiers



Max-
Sonnen



STAR 1000
visible CMOS-APS sensor

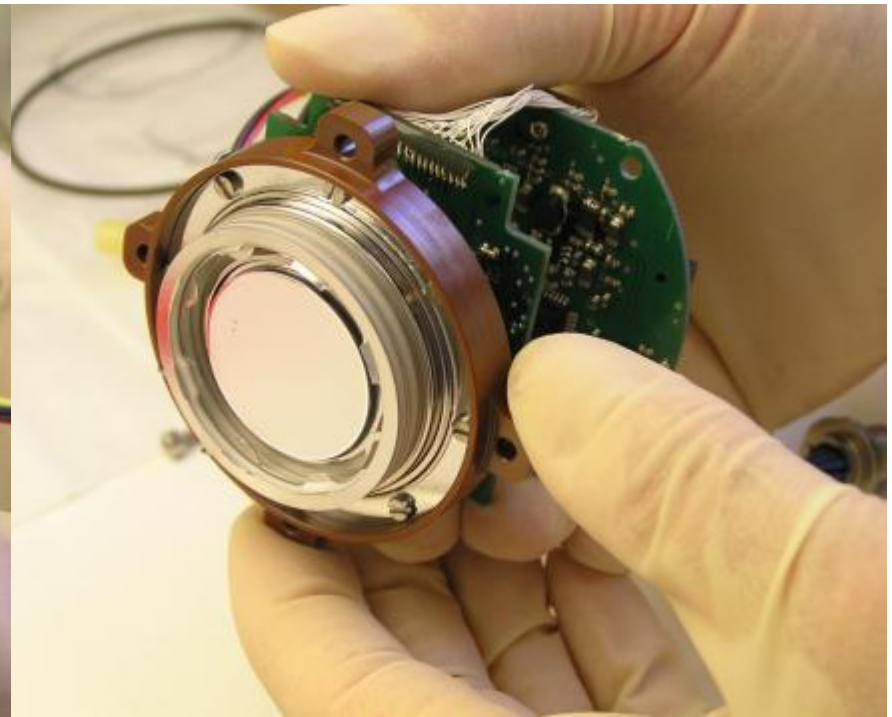


MCP stack

fiber optic blocks

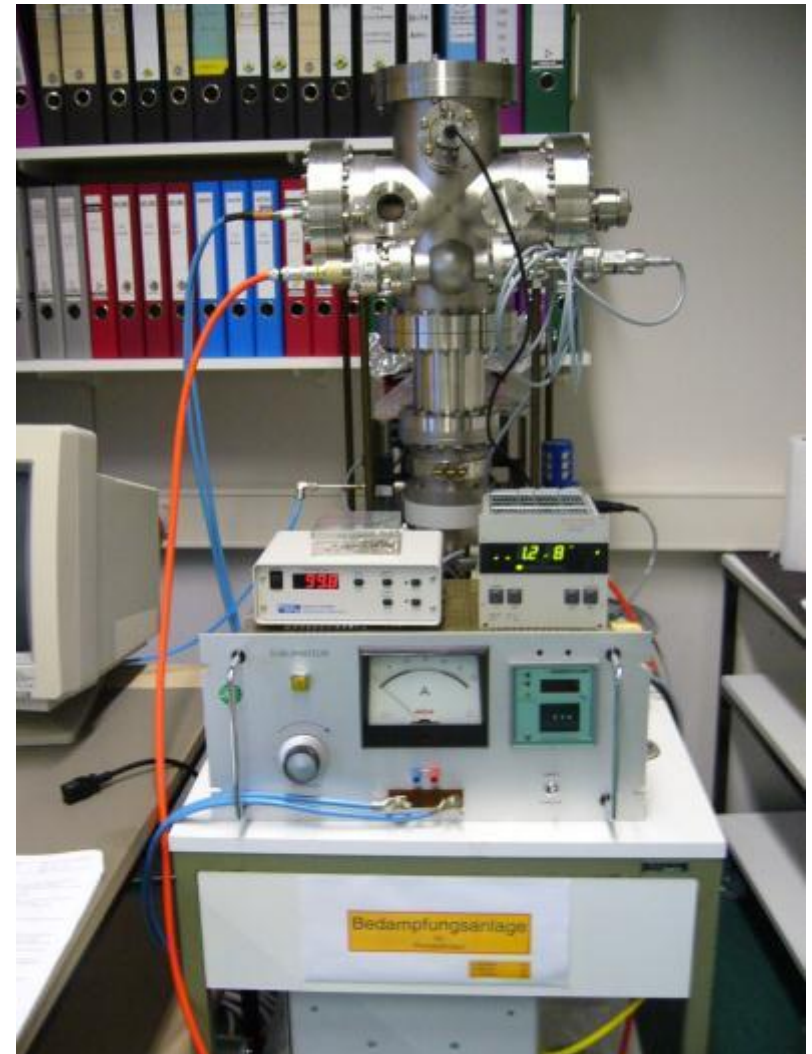
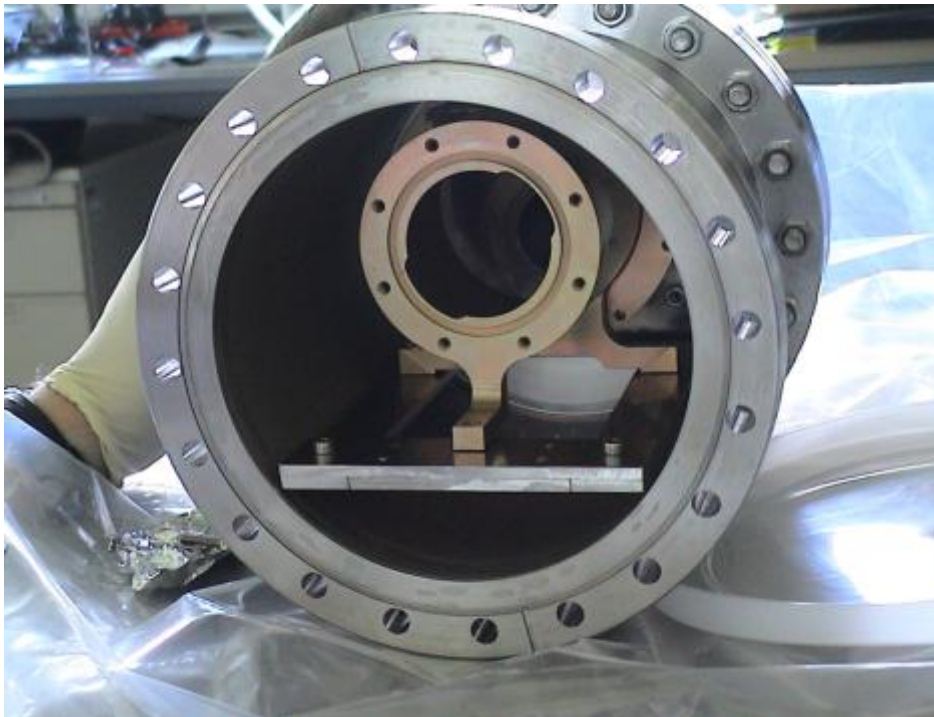
APS sensor board

FEE board



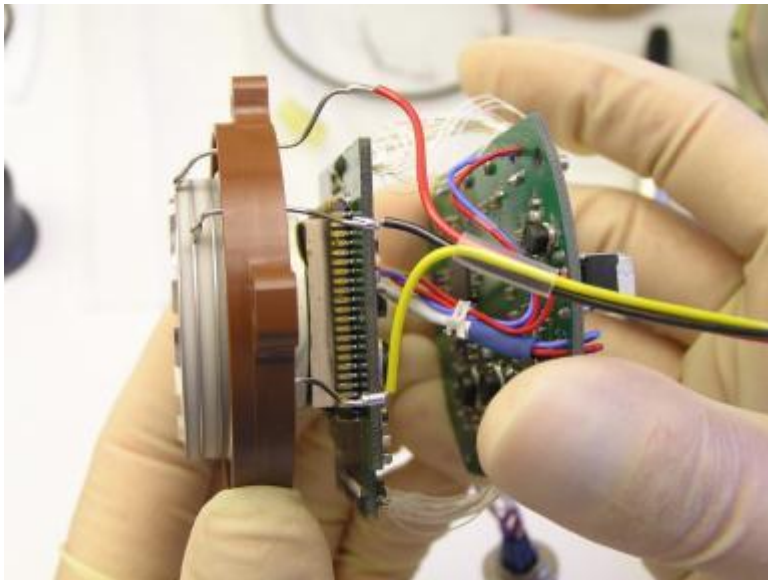
Photocathode deposition chamber at MPS

- done deposition of CsI and KBr up to thickness of 1000 nm with 1 nm resolution

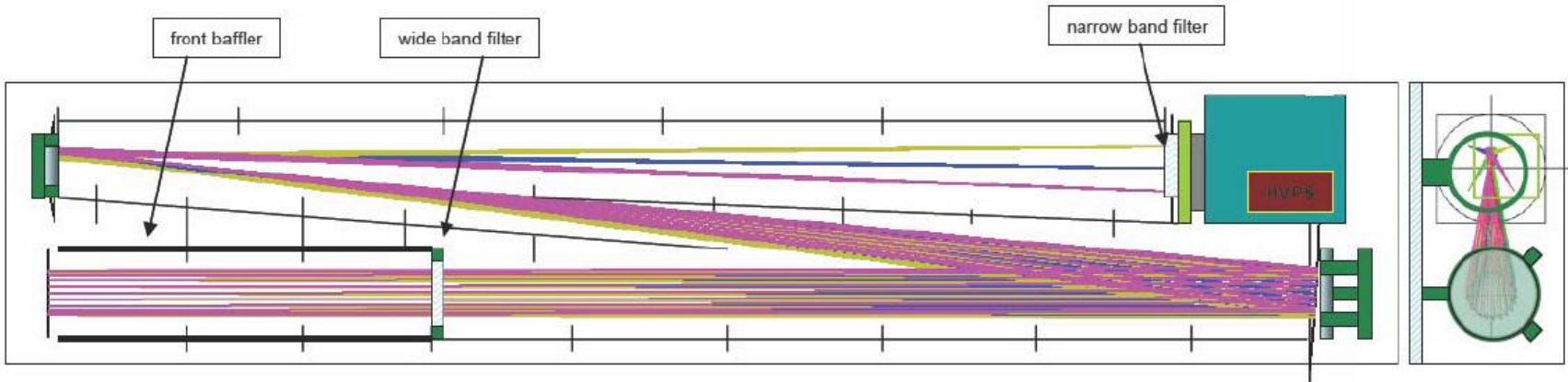


R&D activities: Development of I-APS detector

- intensifier based on microchannel plates with KBr photocathode coating
- coupling with active pixel sensor (APS)
- APS electronic readout circuitry
- space qualification: vibration, acoustic, thermal, radiation hard

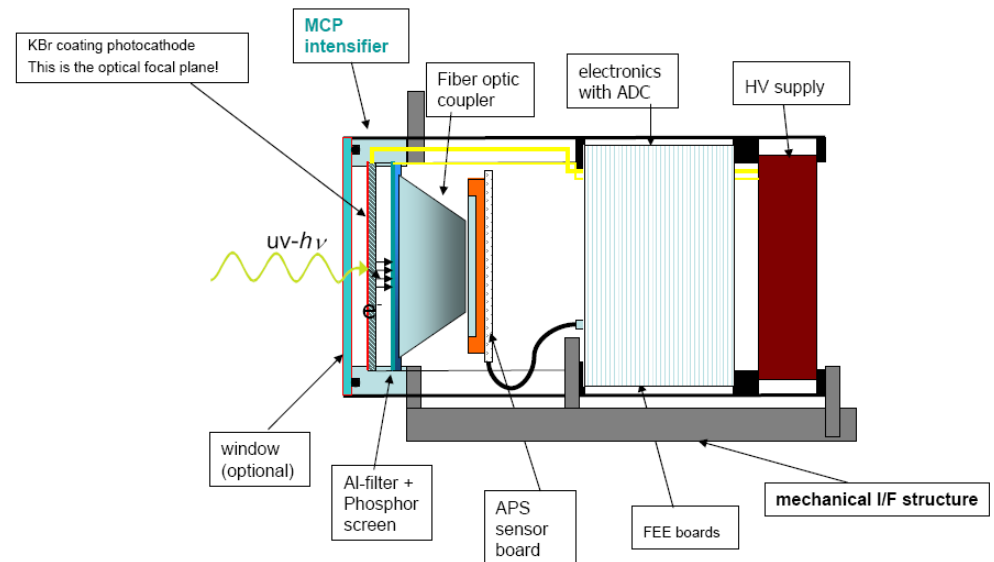


Solar Orbiter EUI HRI_{Ly- α} detector

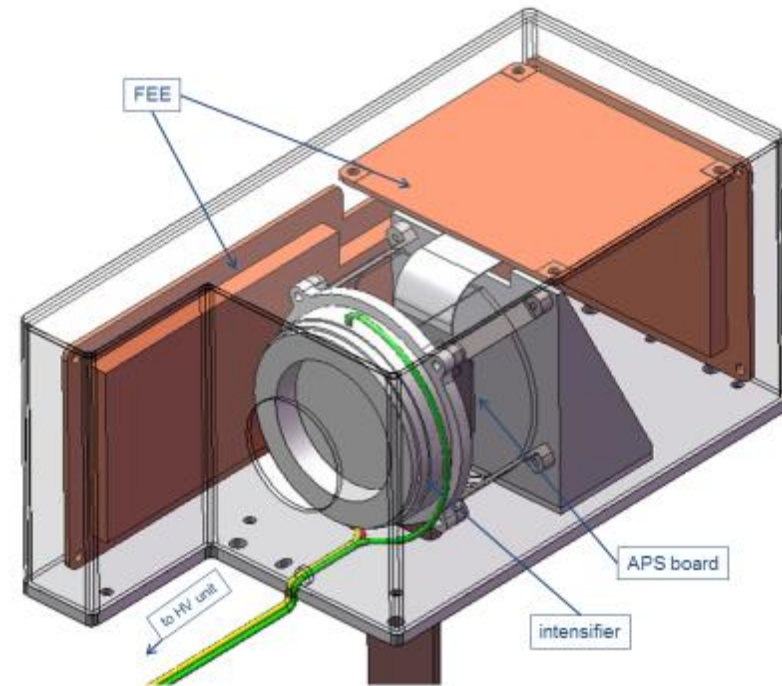
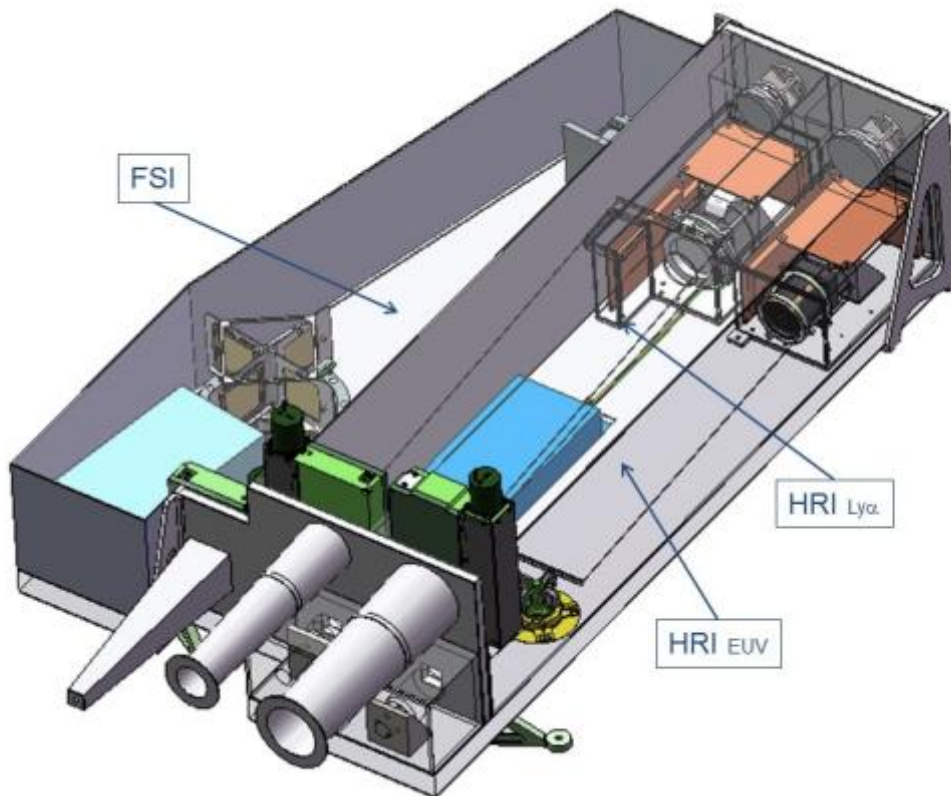


The Lyman- α detector:

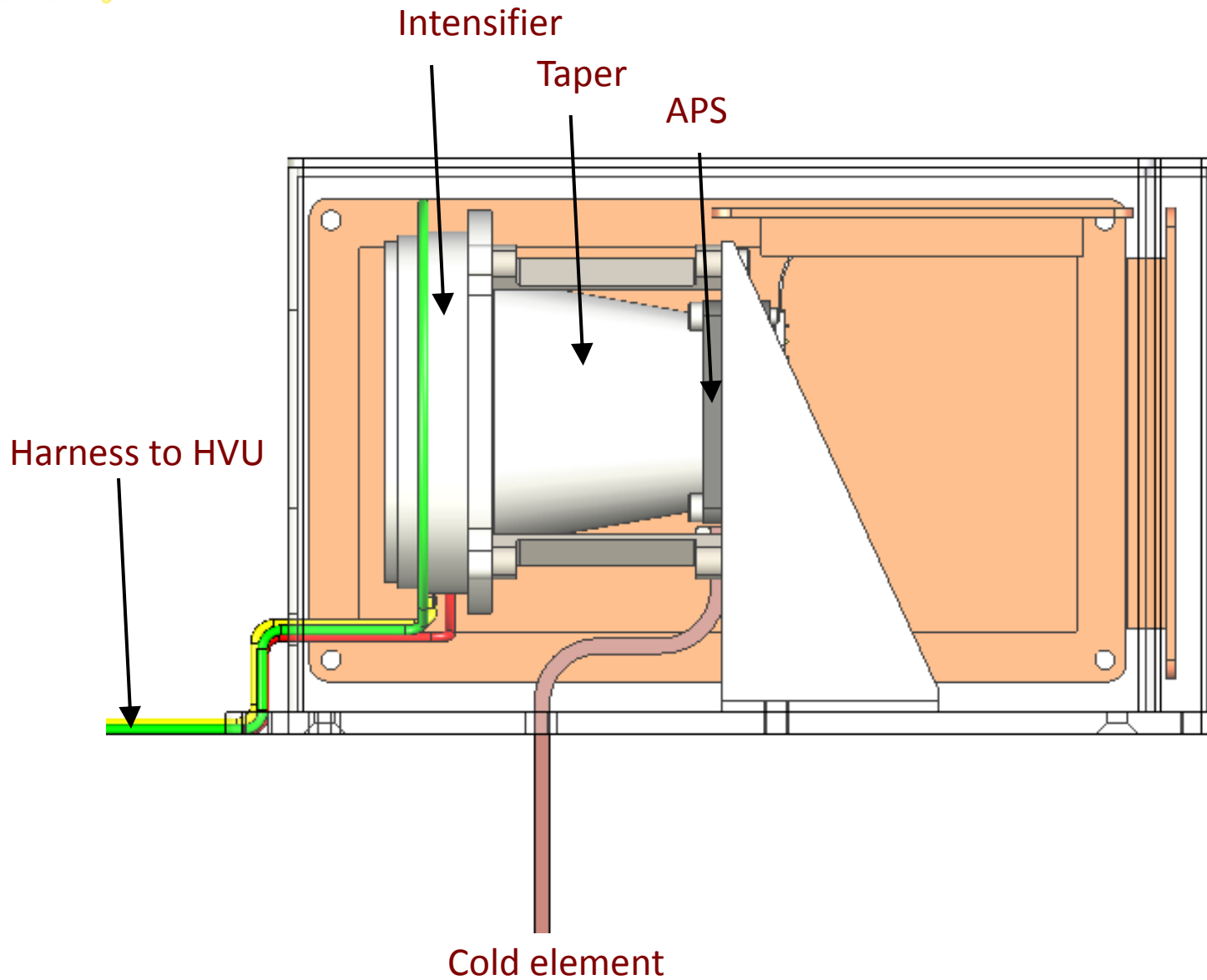
a solar-blind intensified
CMOS/APS camera



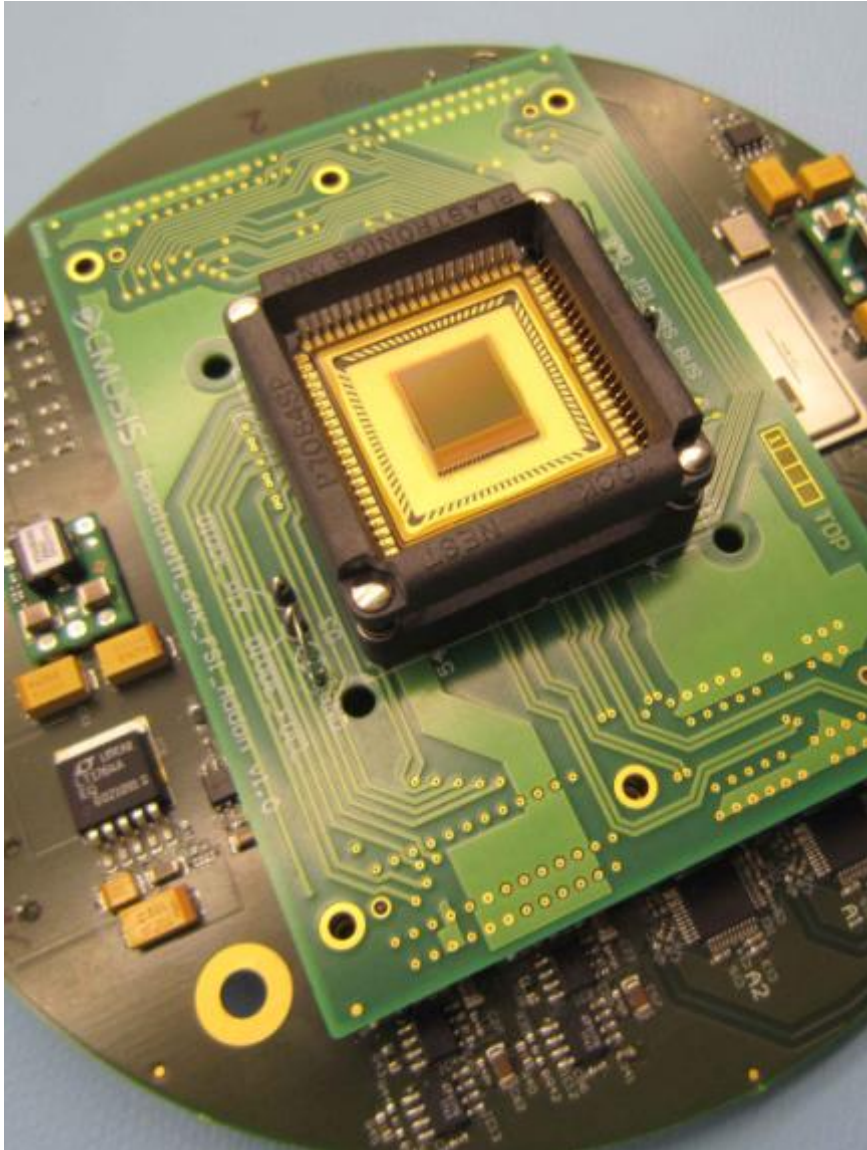
EUI camera



EUI camera



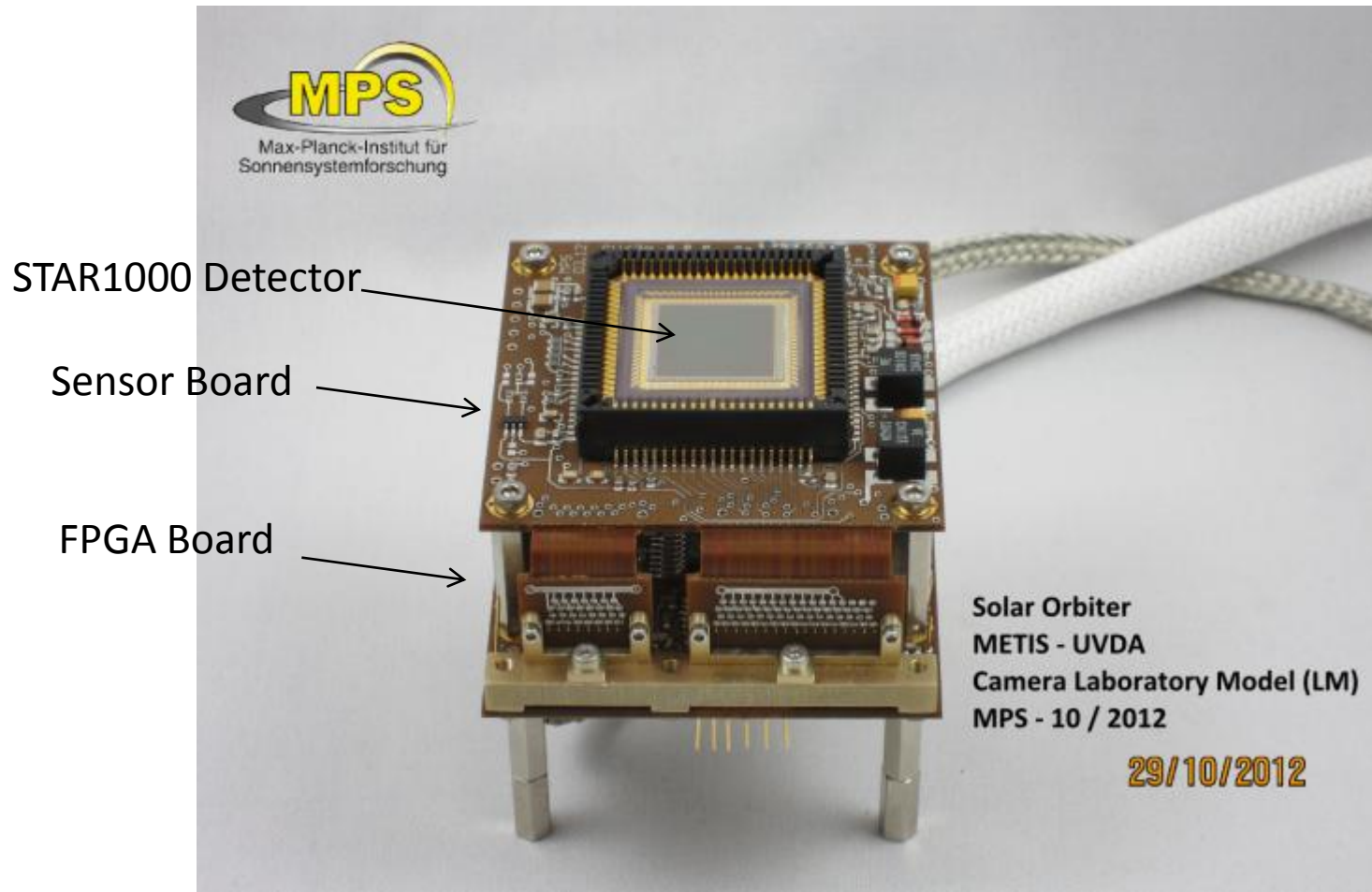
APSOOLUTE sensor prototype
developed by CMOSIS



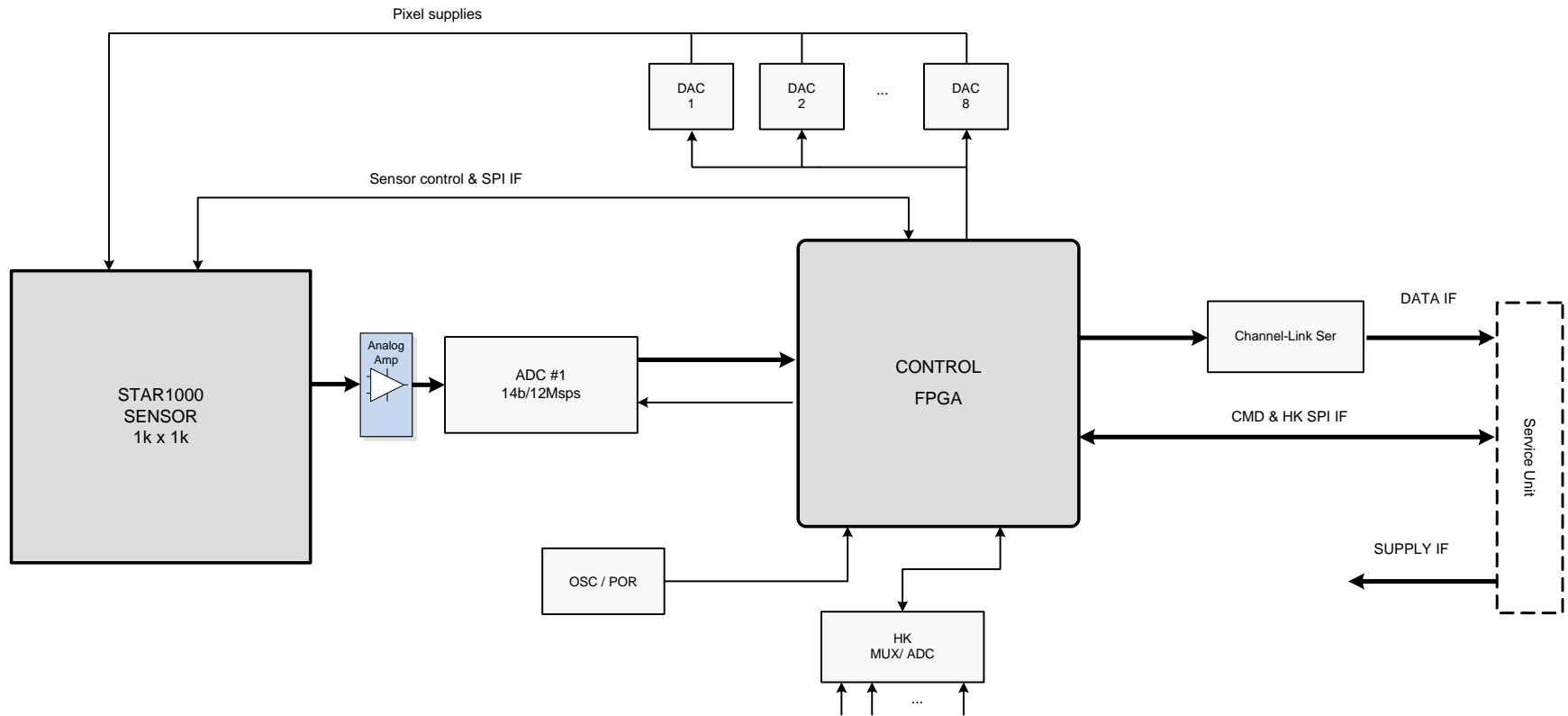
intensifier prototype
developed by PROXIVISION
(KBr photocathode)



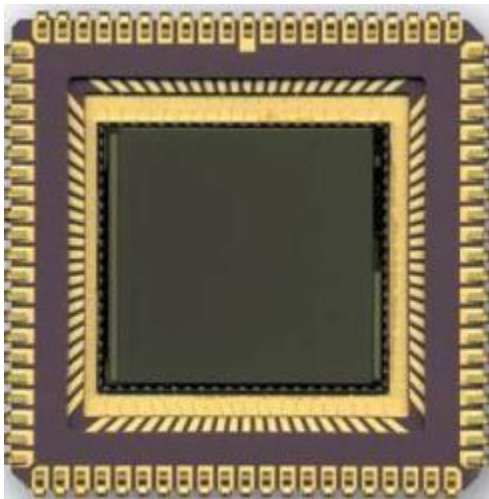
METIS UVDA Camera Electronics



METIS UVDA Camera Electronics: Block Diagram



METIS UVDA Camera Electronics: STAR-1000 sensor



1k x 1k
15 x 15 μm^2

Parameter	Specification	Notes
Detector technology	CMOS Active Pixel Sensor	
Pixel structure	3-T active pixel	Rad tolerant pixel design
Sensitive area format	1024x1024 pixels	
Pixel size	15x15 μm^2	
Pixel output rate	12 MHz	
Windowing	x- and y- addressing random programmable	
Electronic shutter	Rolling shutter, Range 1:1024	
Total dose rad. tolerance	> 250 krad/Si	
Proton radiation tolerance	$\geq 2.4 \times 10^{11}$ proton/cm ² @60 MeV	
SEU tolerance	>127.8 MeV cm ³ mg ⁻¹	
Spectral range	400 – 1000nm	
Quantum efficiency x fill factor (450 to 750nm)	$\geq 30\%$	
Full well charge	135.000 e ⁻	
Linear range (within 1%)	95 ke ⁻	
Supply voltage	5V	digital inputs are 3.3V compatible
Lid	Windowless	

Proton DD: Quantum efficiency losses (~35% red) !

METIS UVDA Camera Electronics

14-Bit ADC, ENOB = 11.5 Bits, 69.2 dB dynamic range (DR)

STAR1000 Temporal Noise: $\sim 1.2\text{mV}$ \rightarrow 9.2DN @14 Bit : ~ 65 dB DR

\rightarrow dynamic range of camera electronics: > 65 dB

- Use of external ADC
- Improved cleanliness of voltage supplies
- Adjustable detector voltages
- Optimized PCB layout
- Optimized ADC sampling (pipeline delay adjustable)
- Use of Space qualified parts while maintaining perf.
- Data transfer using Gray Code

METIS UVDA Camera Electronics: Power Supply Requirements

Supply Voltage ID	Nominal Level [V]	Tolerance	Ripple	Maximum Rise Time [ms]	Nominal Current [mA]	Peak Current (<5ms)	Input Capacitance [μ F]
VCCI	5.15	$\pm 5\%$	<1%	≤ 50	123	TBD	130
VSSI	-5.15	$\pm 5\%$	<1%	≤ 50	82	TBD	15
VCCD	3.3	$\pm 5\%$	<1%	≤ 50	76	TBD	30
VCCA	2.5	$\pm 5\%$	<1%	≤ 50	83	TBD	15

METIS UVDA Camera Electronics: Power & Mass

Power (measured on LM):

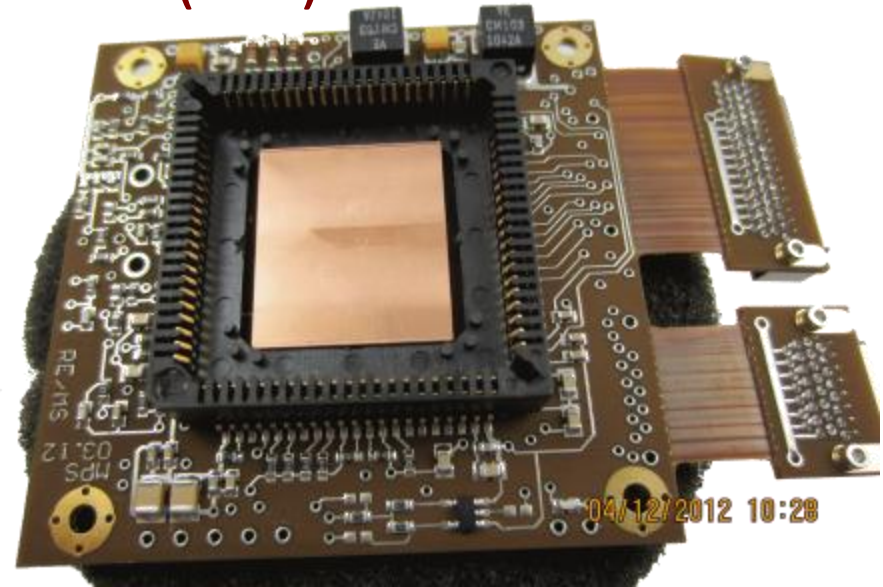
	Unit	+5.15V (V_{CCI})*	-5.15 V (V_{SSI})*	+3.3 V (V_{CCD})	+2.5 V (V_{CCA})	Total Power (W)	Power incl. 20% contingency
12 MHz	mA	102	-68	63	69	1.26	1.51
Stand-by	mW	525.3	350.2	207.9	172.5		

Mass (measured on LM):

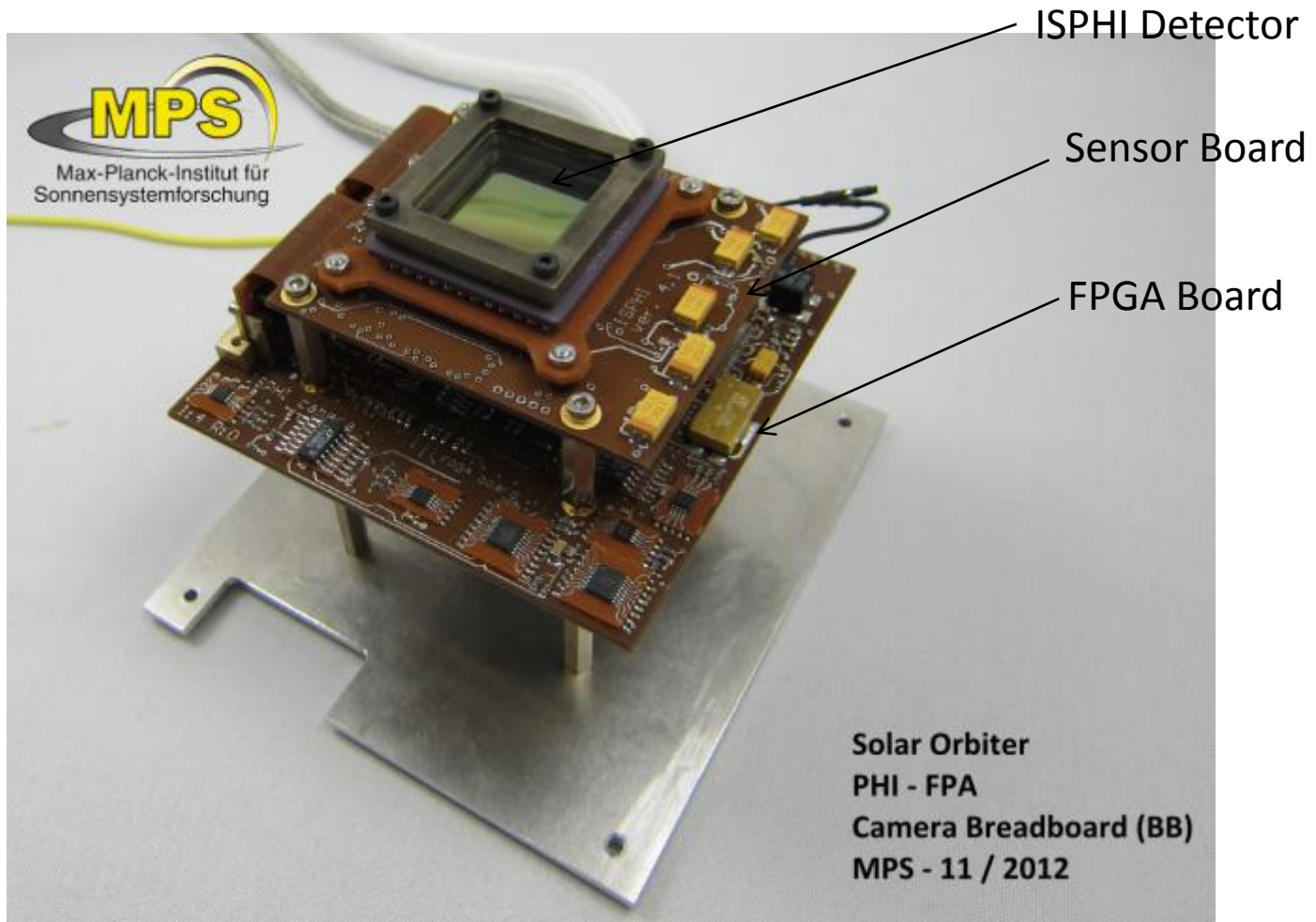
Item:	Mass [g]:	Remark:
Sensor Board (incl. Sensor)	48	
FPGA Board (incl. FPGA)	70	
Cold Finger (copper stamp)	29	
Total incl. 10% contingency:	161.7	I/F harness not included !

METIS UVDA Camera Electronics

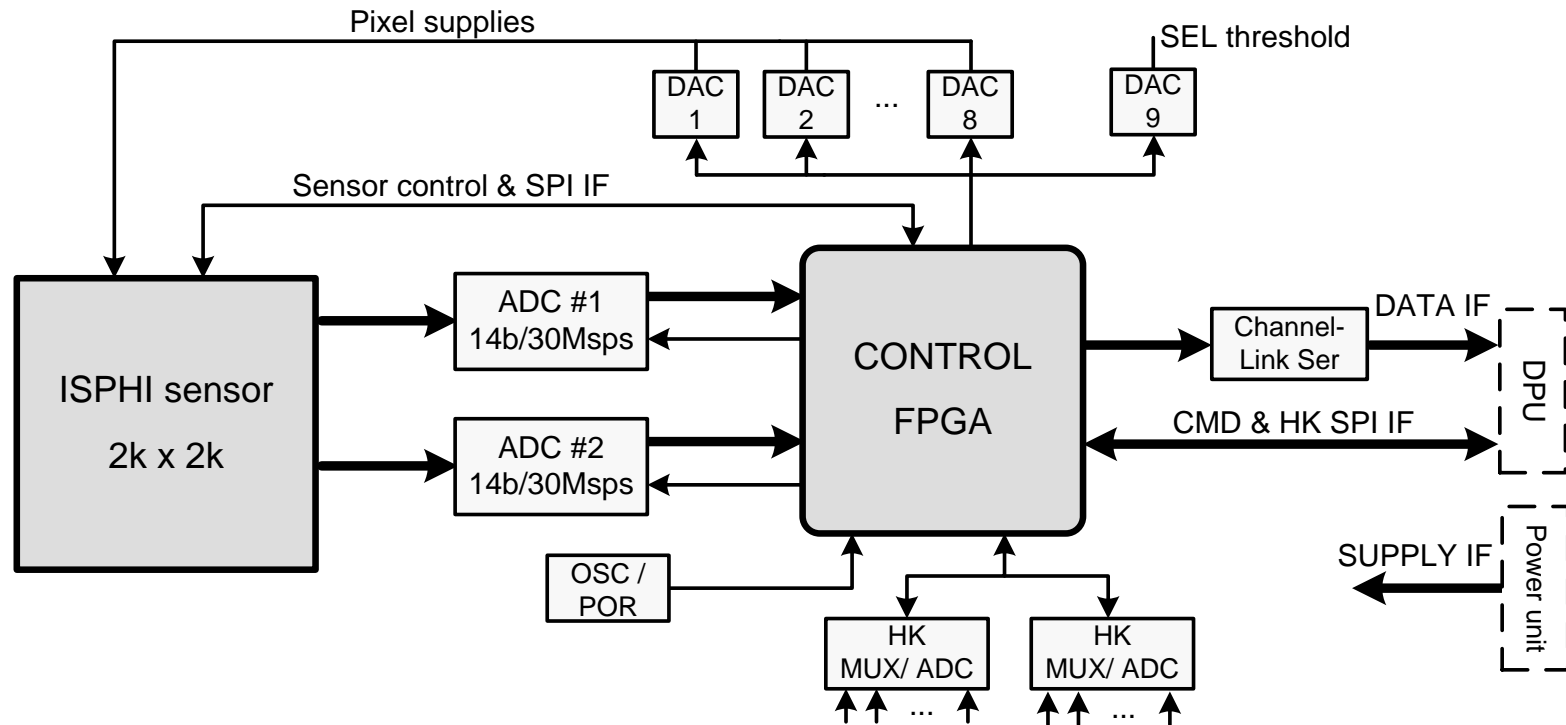
- radiation tolerant design (SO Specs.)
- channel link LVDS I/F
- LM – working, electrical testing in progress
- Cold Finger concept under test (PHI)
- planned LM delivery:
End of Jan. 2013



SO-PHI FPA Camera



ISPFI FPA block diagram



SO-PHI FPA Camera

- 2kx2k ISPHI sensor 10 fps readout
- channel link high speed LVDS I/F
- radiation tolerant design (SO Specs.)
- BB model ready, tested in TV
- external power supply – clean supply mandatory for performance !

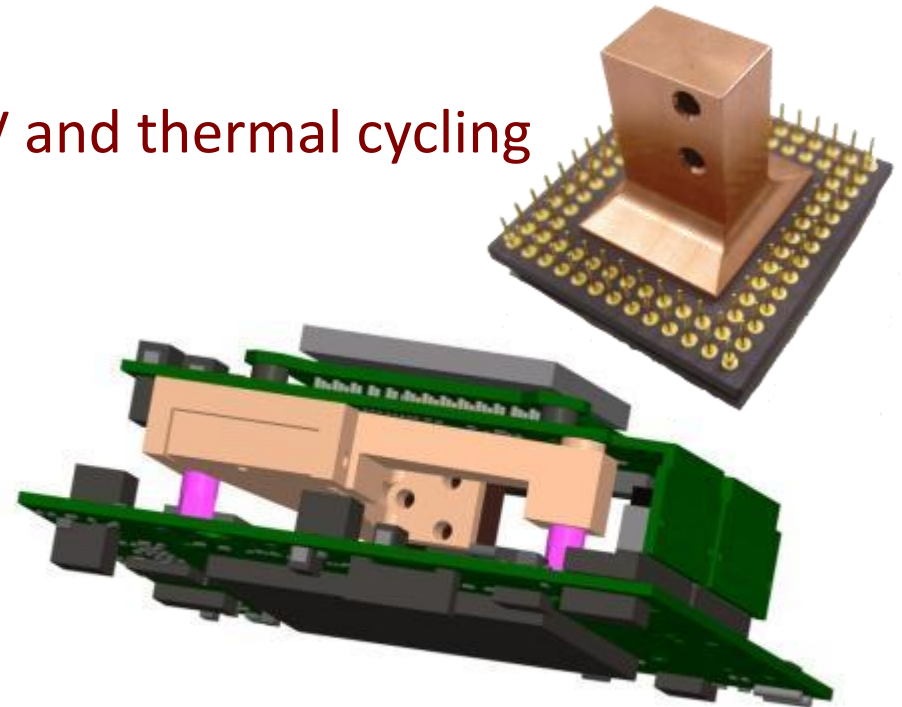
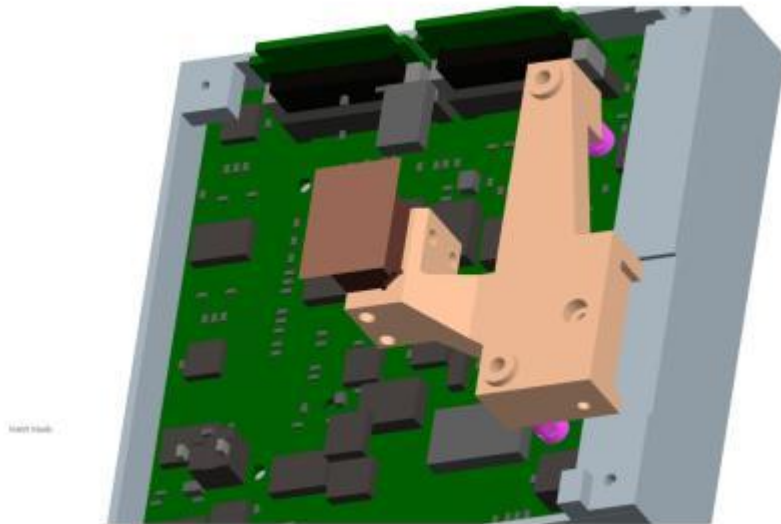
SO-PHI FPA Camera: Power and Mass

	Unit	+5.15V (V _{CCI})*	-5.15 V (V _{SSI})*	+3.3 V (V _{CCD})	+2.5 V (V _{CCA})	+1.5 V (V _{CCB})	Total Power (W)	Power incl. 20% contingency
15 MHz Stand-by	mA	50	-30	170	70	20	1.18	1.41
	mW	257.5	154.5	561	175	30		
15 MHz Acquiring	mA	50	-30	240	75	22	1.43	1.72
	mW	257.5	154.5	792	187.5	33		
30 MHz Stand-by	mA	50	-30	180	80	34	1.26	1.51
	mW	257.5	154.5	594	200	51		
30 MHz Acquiring	mA	50	-30	280	90	36	1.62	1.95
	mW	257.5	154.5	924	225	54		

Item:	Mass [g]:	Remark:
Sensor Board	64.2	
FPGA Board	37.5	
Cold Finger (copper stamp)	70	
Total:	171.7	

SO-PHI FPA Camera: Cold Finger Concept

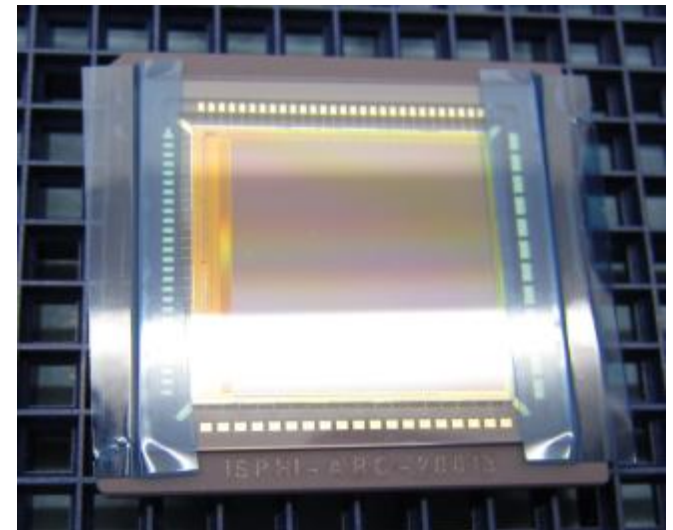
- Copper stamp glued to sensor back
- Interface to instrument cold finger has to provide mechanical and thermal stress relief
- design under test at MPS in TV and thermal cycling



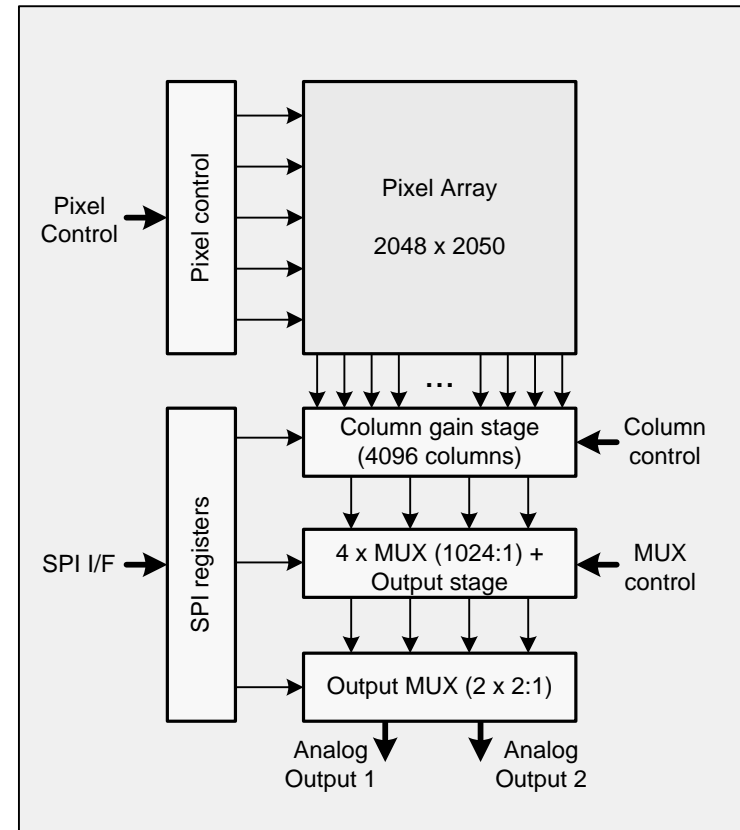
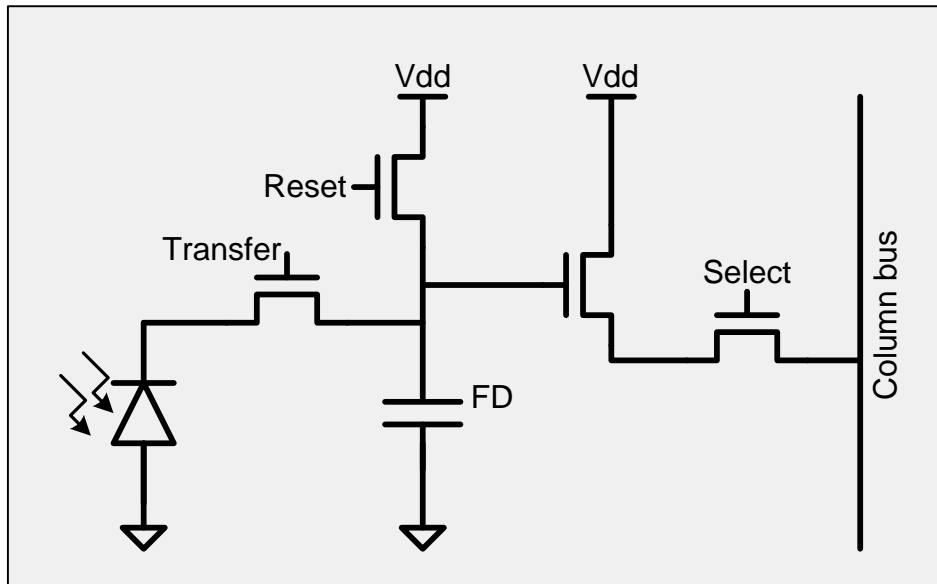
CMOSIS ISPFI Rev. B

APS 2k x 2k, two analog outputs,
30 MHz 10 fps high speed readout, rolling shutter
no windowing capability in rows !

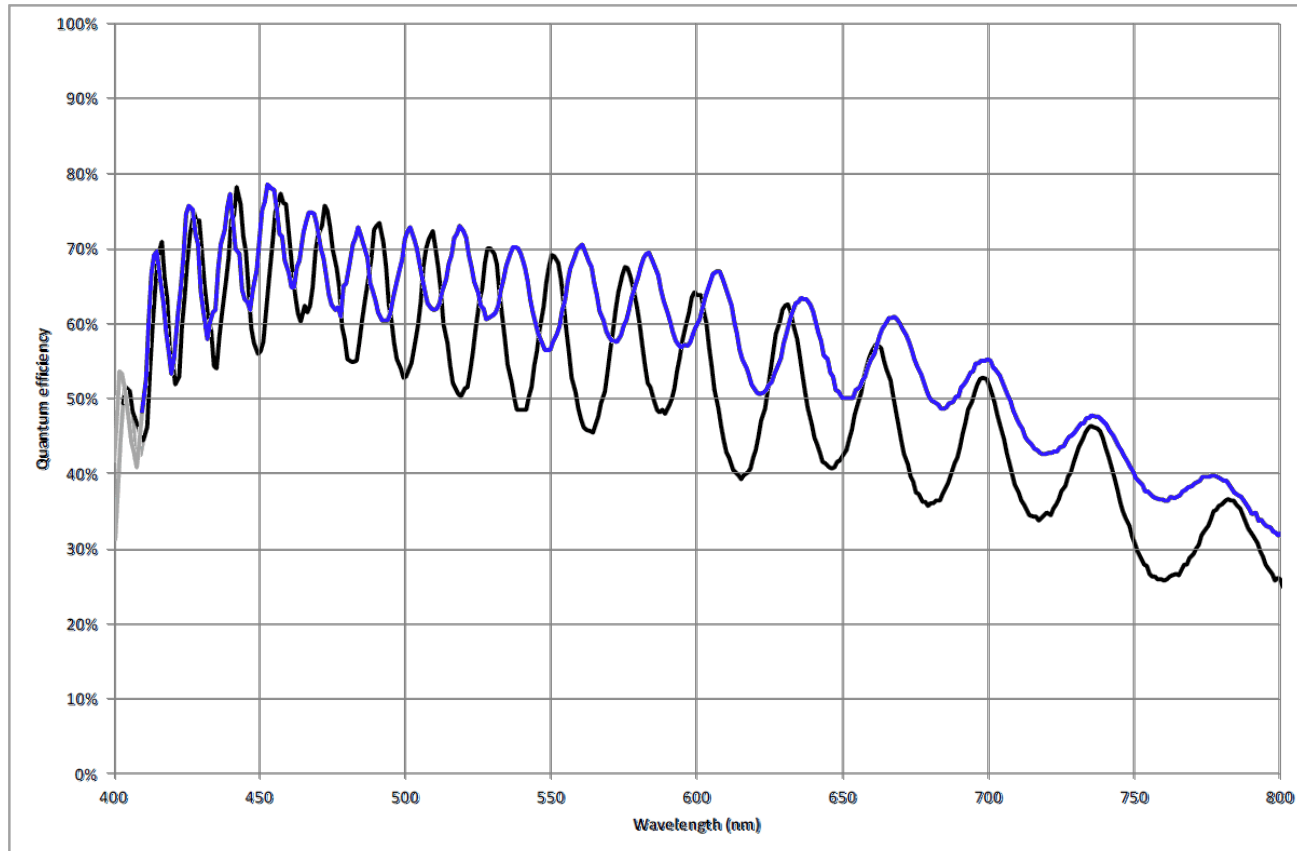
Parameter		Value
Frame rate	fps	10
Full Well	ke ⁻	(60) 90
Dark noise @ RT	e ⁻	57
Dark current (293 K)	e ⁻ /s	90 (TBC)
Sensitivity (617nm)	%	42 – 60
Non-linearity	%	< 2
PRNU (local)	%	1.4
Power consumption	mW	500



ISPHI Pixel architecture



ISPHI: Quantum Efficiency



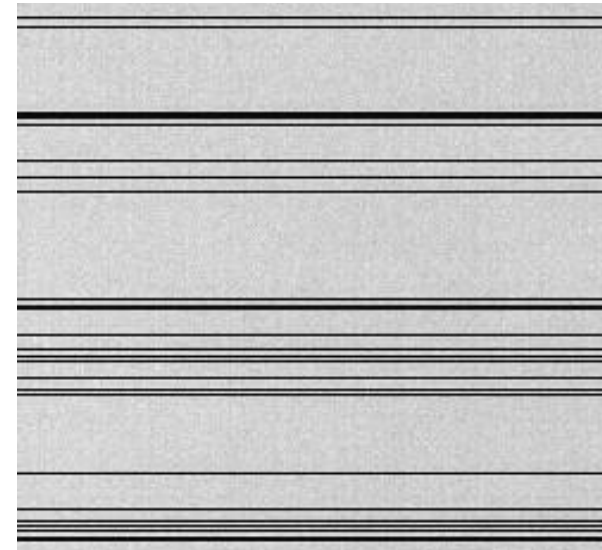
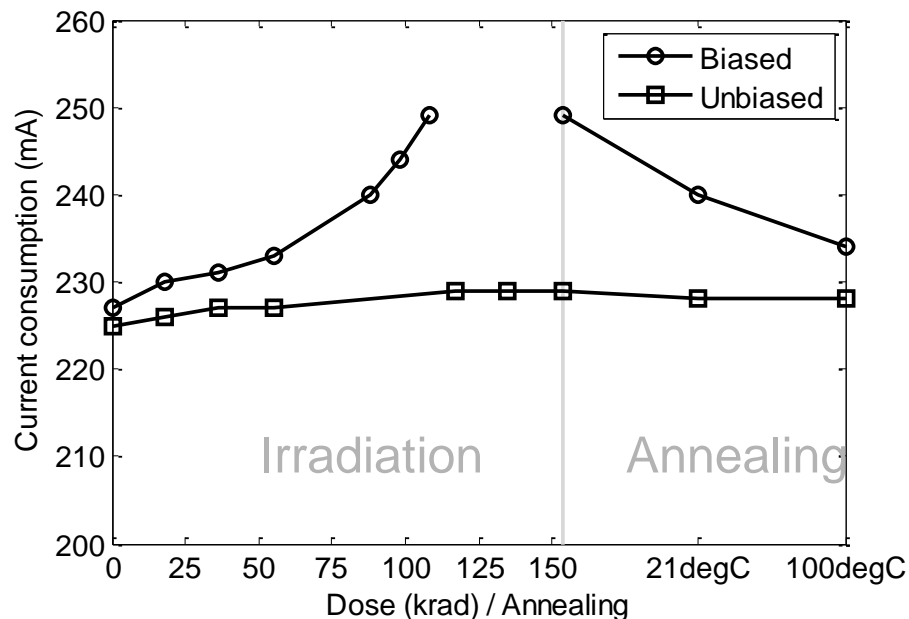
- Spectral and spatial fringing due to interferences on dielectric stack on top of the photodiode
- ARC coating is applied on Rev. B devices for improvement (blue)

CMOSIS ISPHI Radiation Tests

- Radiation tests performed
 - Total Ionizing Dose up to 154 krad(Si)
CRC, Lovaine-La-Neuve, Aug. 2011
 - Displacement Damage at 10, 15, 20 MeV ($4 \cdot 10^{11}$ p⁺/cm²)
LIF, IPNAS Liège, Nov. 2011
 - Single Event Effects pre-assessment with Californium-252
ESA/ESTEC, Summer 2012

ISPHI: TID radiation tests results

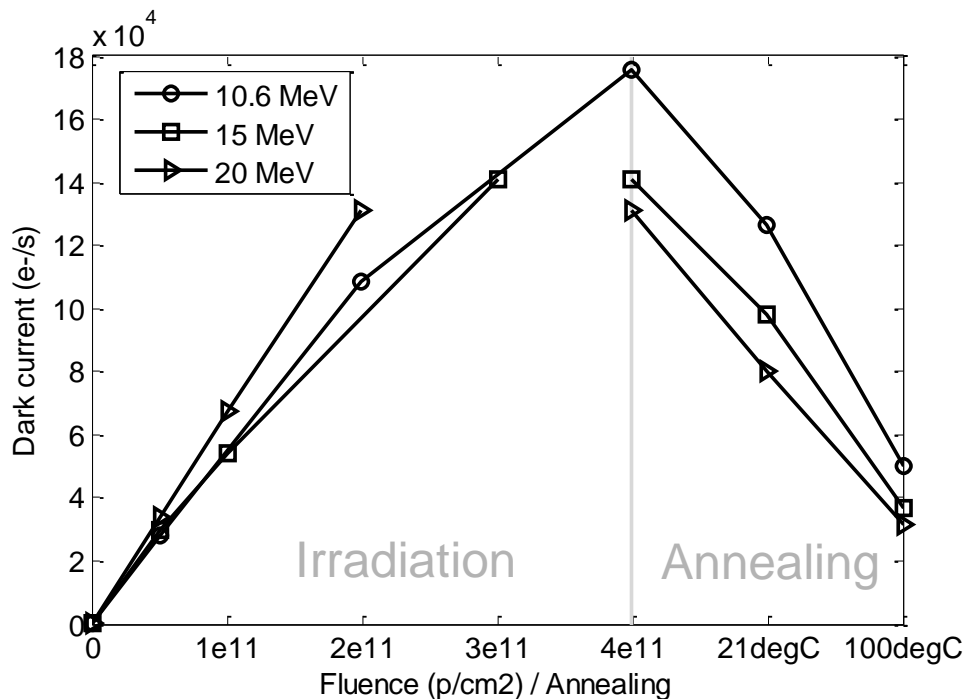
- Sensor is radiation tolerant up to 75 krad(Si)
- Minor degradation on dark current, dark current non-uniformity, consumption and sensitivity
- Annealing helps recovering affected parameters



row defects above 75 krad(Si)

ISPHI: Proton DD radiation tests results

- Permanent damage on 2 parameters
 - Dark current and Dark current non-uniformity
- Temporal damage on sensitivity, PRNU and consumption



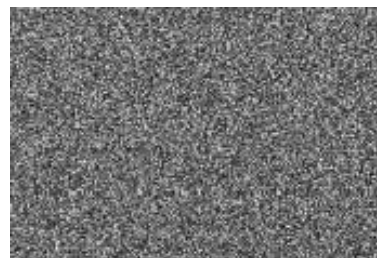
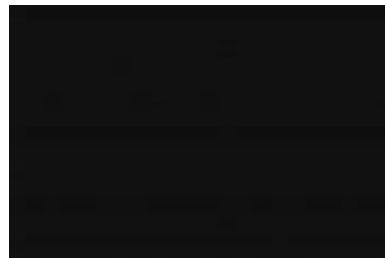
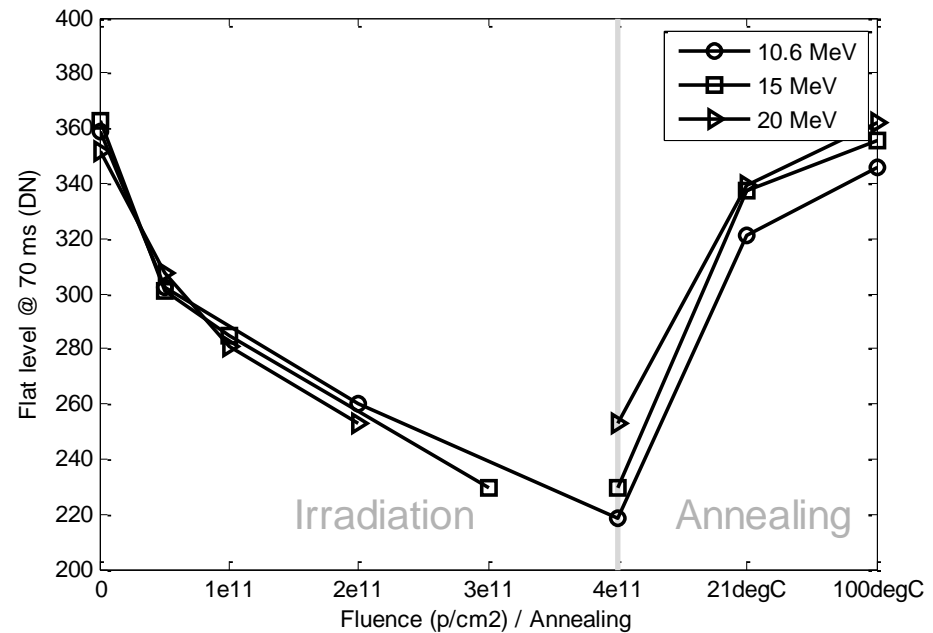
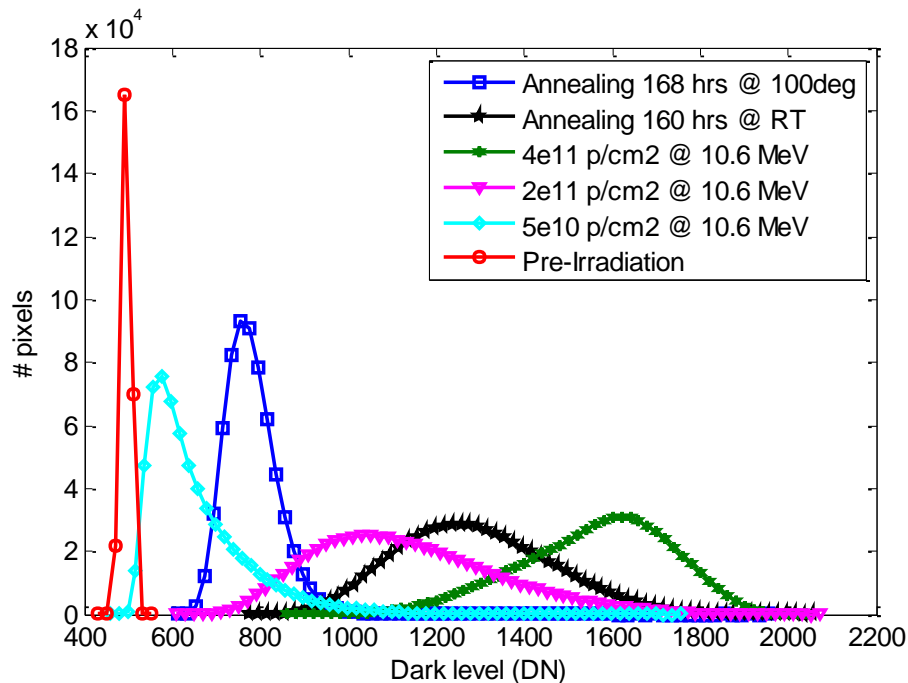
200 → 10⁵ → 5 · 10⁴ e⁻/s

To deal with it:

- Lower temperature
- Short exposures
- Annealing helps
- Exp. lower fluence

ISPHI: Proton DD radiation test results

- DC, Dark current non-uniformity and sensitivity after DD

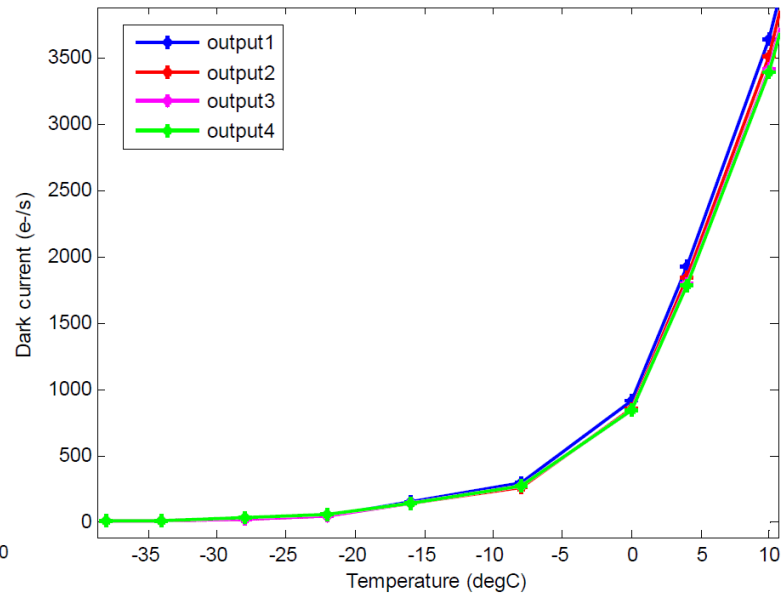
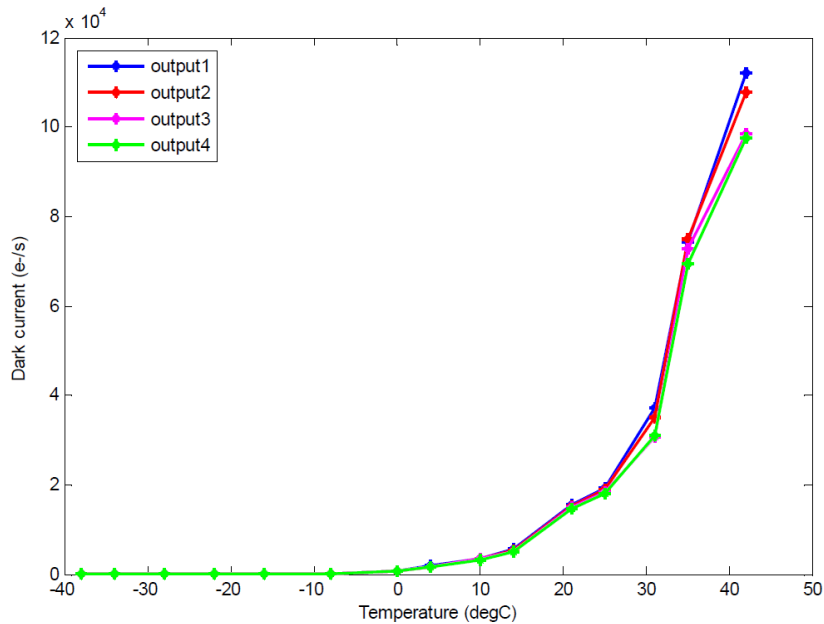


SEE radiation test results

- Cf-252 allows pre-assessment of sensor SEE tolerance
 - Low penetration depth
- No latch-up occurred
- Seven single event upsets were detected
 - Sensor registers are not duplicated
 - Automatic recovery system of FPA electronics tested
- Heavy Ions test planned for Q1/2013

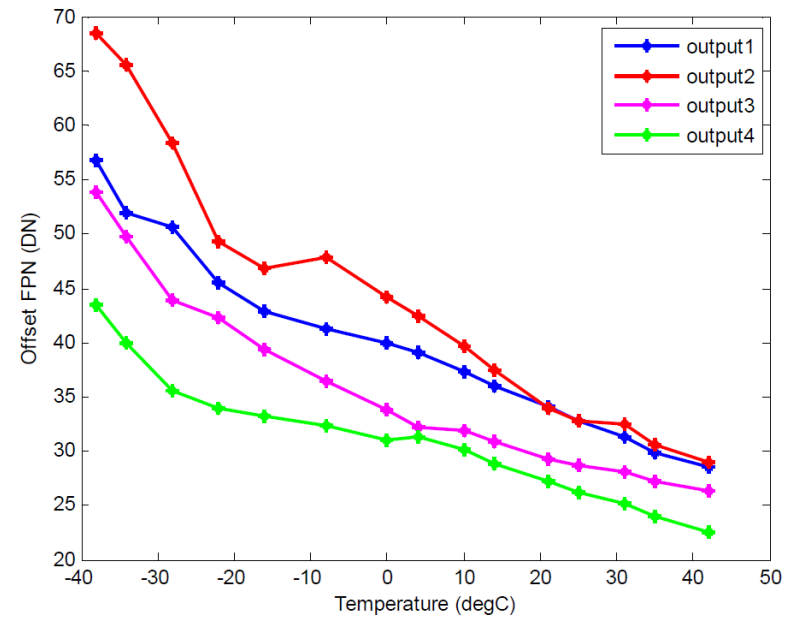
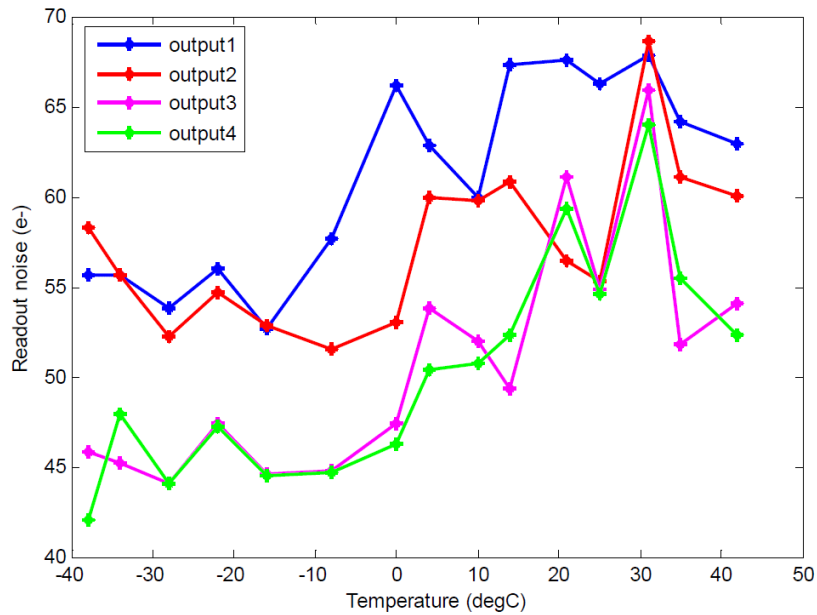
ISPHI Dark Current vs. Temperature

Temperature	-28	-8	0	25	40
Dark current (e ⁻ /s): Post Irradiation	30	272	847	17980	97470
Pre Irradiation				254	



Dark current vs. Temp. ISPHI 10029 a'fter irradiation (10.6 MeV, 4x10¹¹ p/cm², 213.2 krad [Si]² TiD)

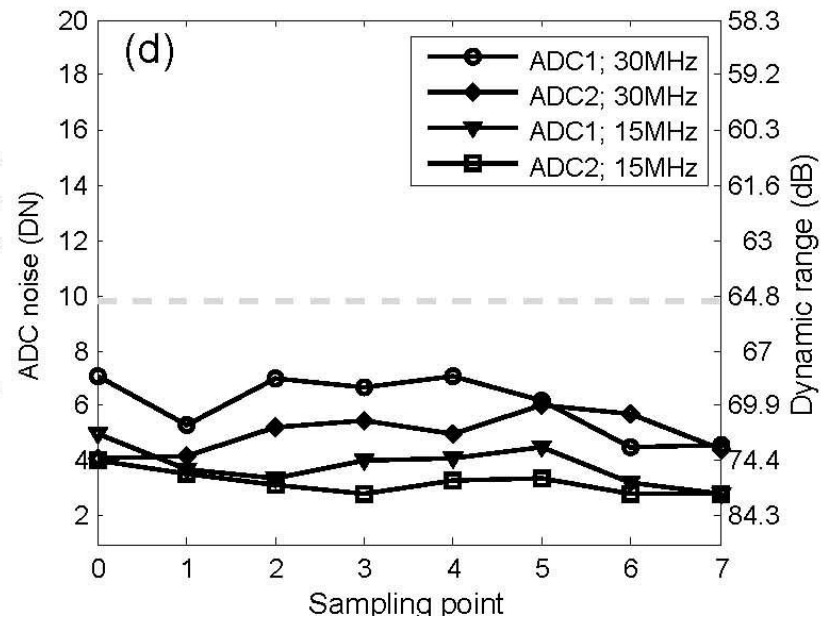
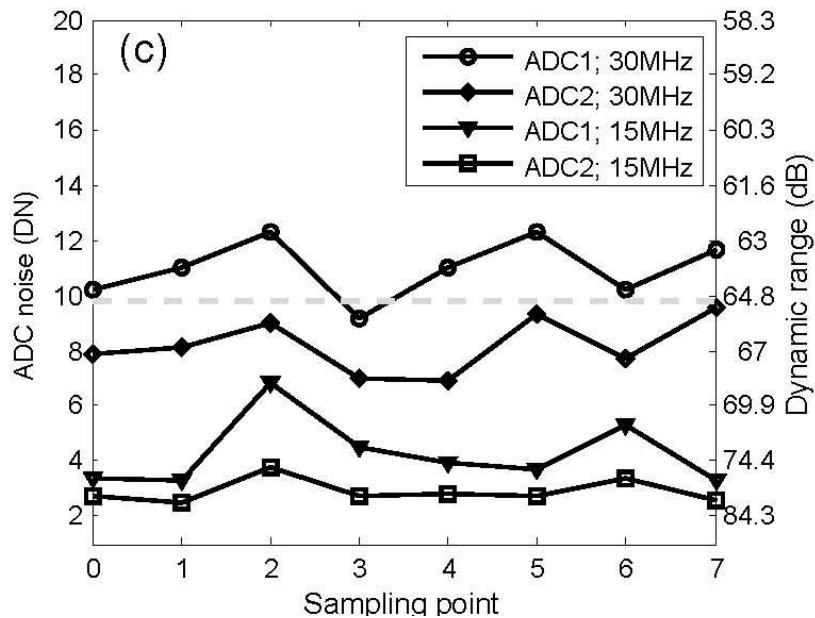
ISPHI Readout Noise and FPN vs. Temp



Readout Noise and FPN, ISPHI 10029 after irradiation (10.6 MeV, 4×10^{11} p/cm², 213.2 krad [Si]² TiD)

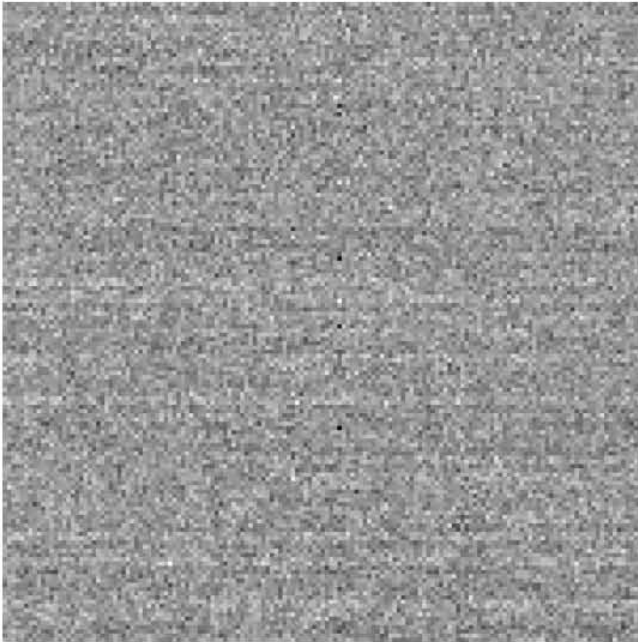
Digitization noise

- Applying fixed input voltages to the ADCs
 - (c): Prototype after removal of interference pattern
 - (d): BB camera



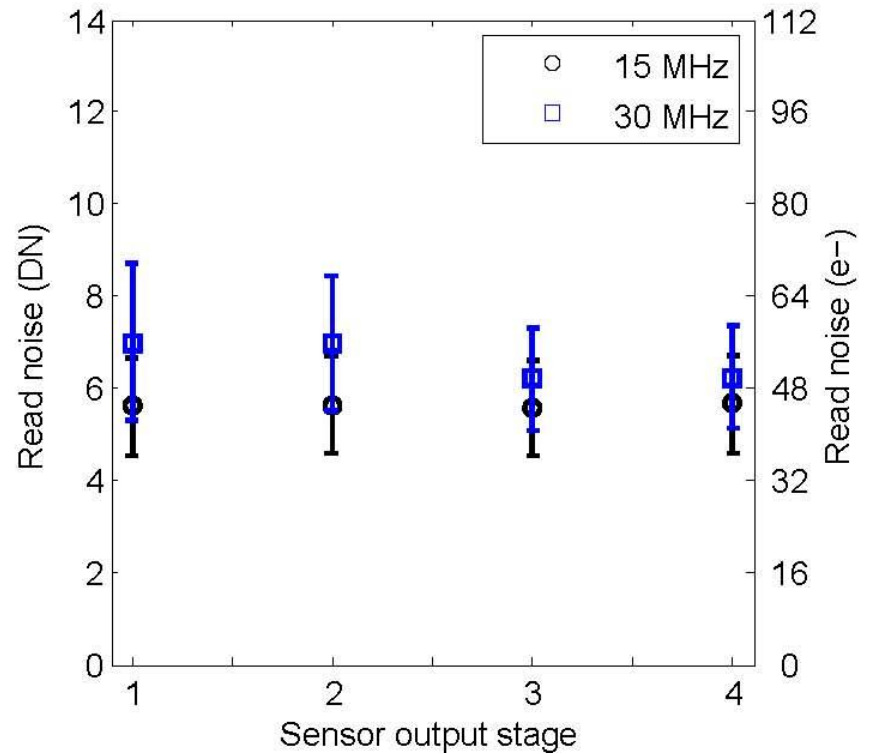
Overall dark noise

- Including ISPHI and camera electronics



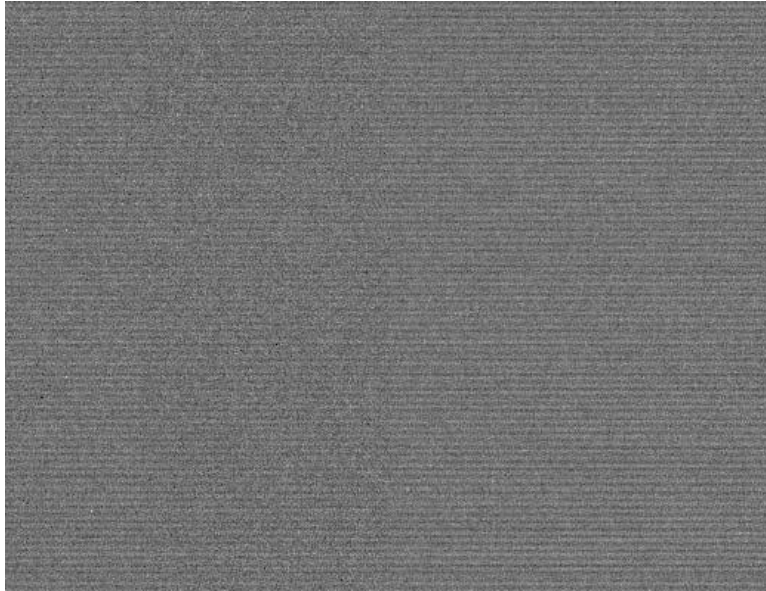
Dark image:

- Shortest exposure
- Subwindow



Total read noise versus output and operating frequency

Dark noise and offset FPN



- Differential dark image
FPN is removed

		Output 1 (DN)	Output 2 (DN)	Output 3 (DN)	Output 4 (DN)
1	Offset FPN	19.1963	17.7866	16.858	16.6184
2	Mean dark noise	7.0072	6.9701	6.1966	6.2409
3	Error bar of 2	2.432	1.8668	1.5192	1.5002

Back-up slides

ISPHv1: performance

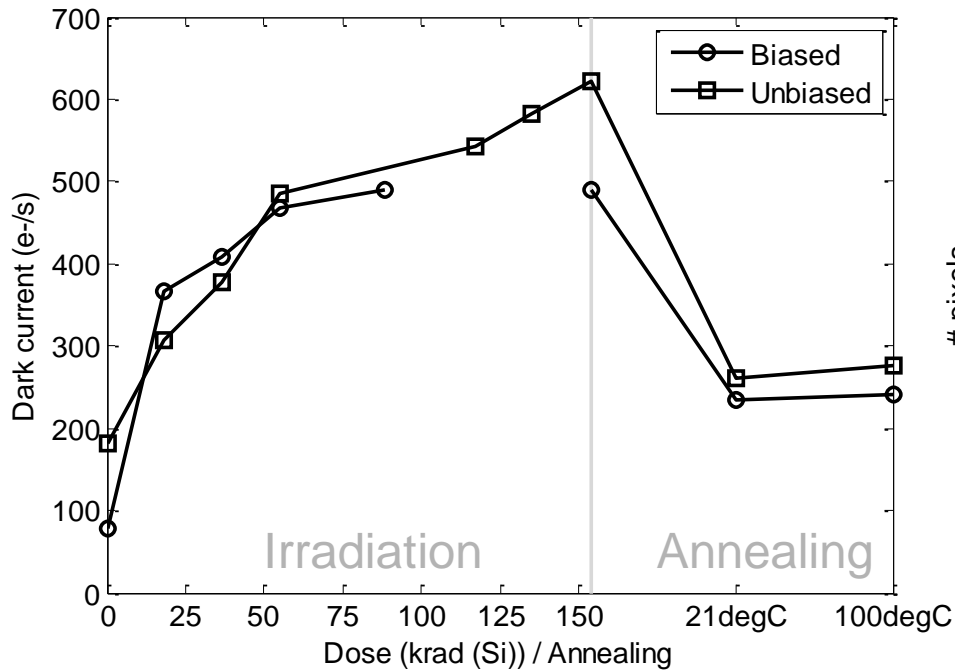
- APS - 2k x 2k on 10 μm^2 pixel pitch
- 4T pixel design with rolling shutter

		Requirement	Result
Frame rate	fps	> 10	11**
Full Well	ke ⁻	> 100	60 – 90
Dark noise	e ⁻	< 100	57
Dark current (293 K)	e ⁻ /s	< 200	90
Sensitivity (617nm)	%	> 50	42 – 60
Non-linearity	%	< 2	< 2
PRNU (local)	%	< 5	1.4
Power consumption	mW	< 500	480

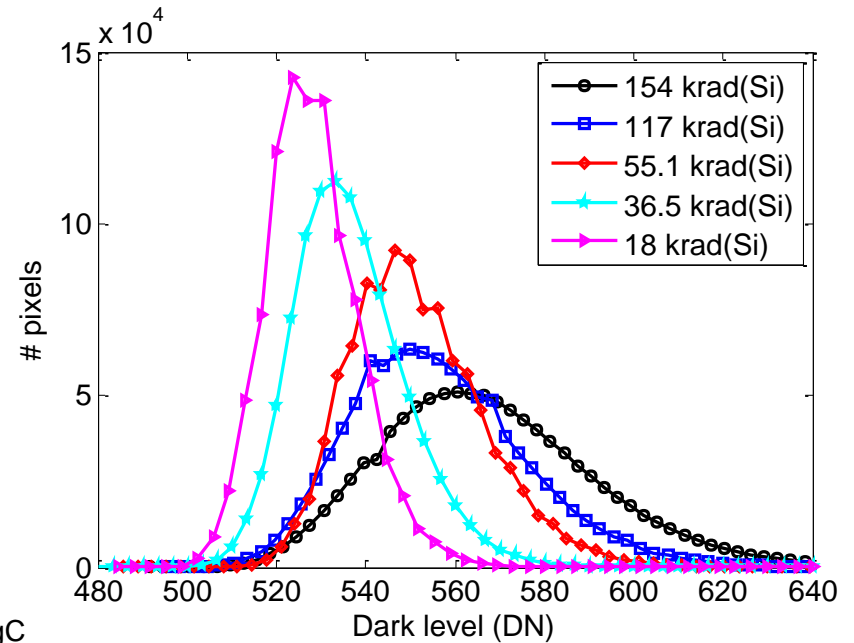
** Ghosting artifacts

ISPHI radiation test results

- Dark current after TID

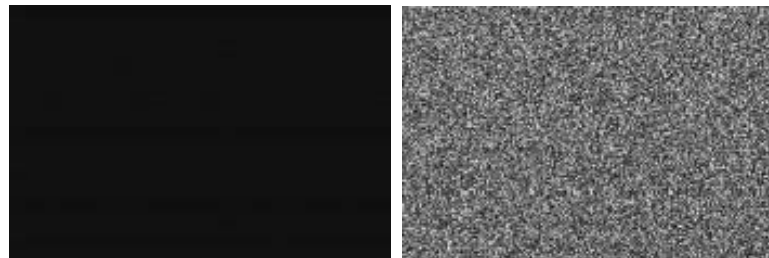
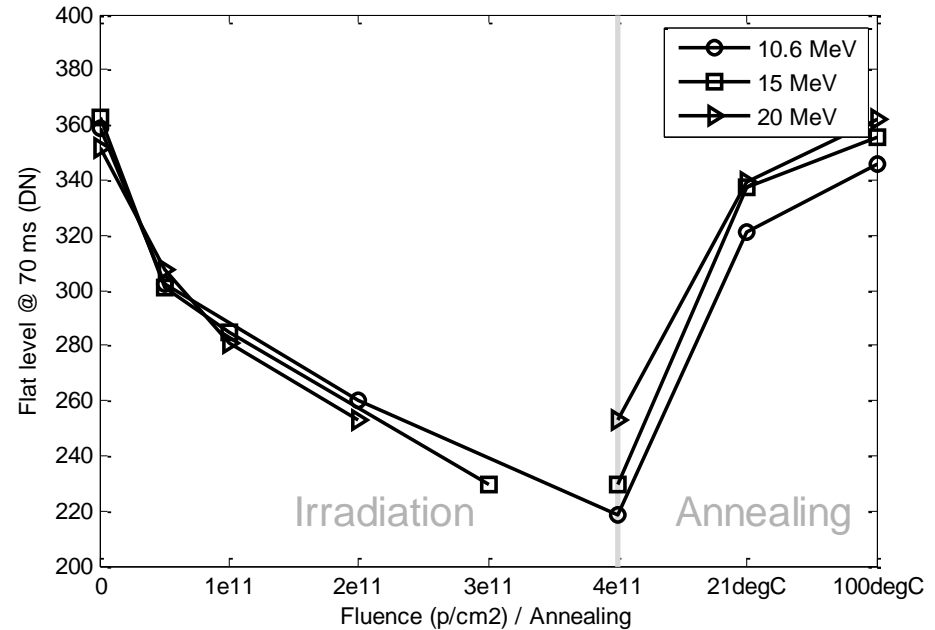
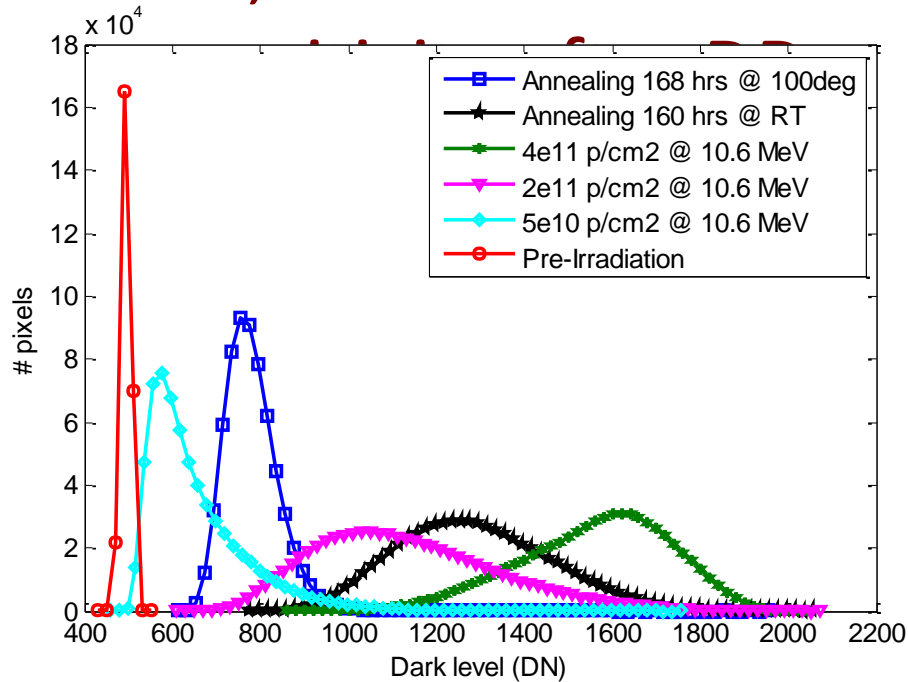


200 → 600 → 280 e-/s



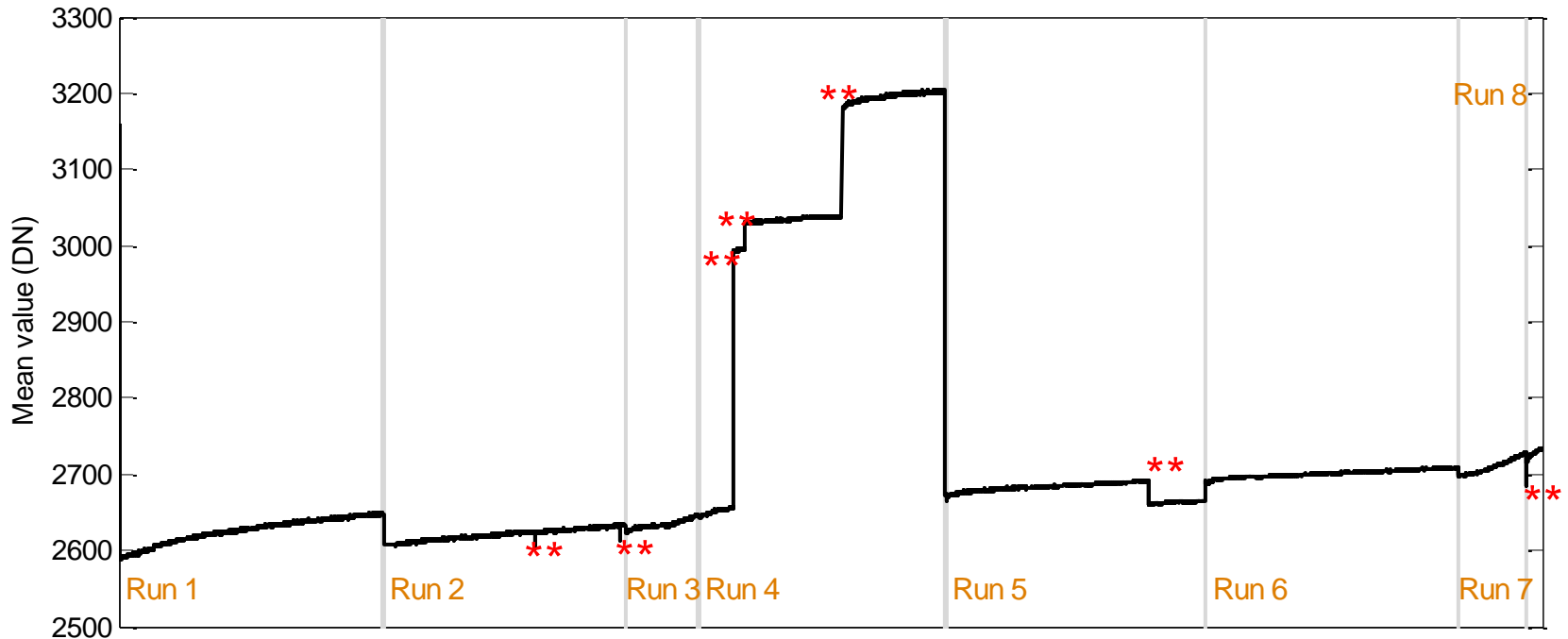
ISPHI radiation test results

- DC, Dark current non-uniformity and

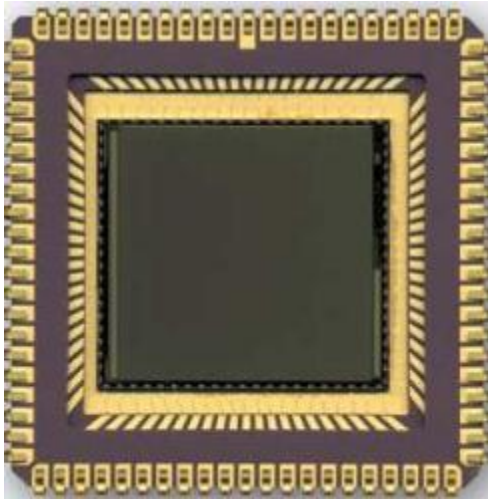


ISPHI radiation test results

- Cf-252 SEE



Back-up: STAR1000



1k x 1k
15 x 15 μm^2

Frame rate	11 fps
Full Well	95 ke ⁻
Readout noise	47 e ⁻
Dark current	3135 e ⁻ /s (+25 ° C)
Shutter	Rolling
Sensitivity	20 % (frontside)
Power cons	100 mW
Radiation hard	230 krad (TID)

Proton DD: Quantum efficiency losses (~35% red)

SO radiation specification

Requirement	Al shield	Value
TID* (Si)	1 mm	150 krad
	2 mm	73 krad
Proton fluence	-	$3.8 \cdot 10^{11}$ p/cm ² at 10 MeV
		$8.8 \cdot 10^{10}$ p/cm ² at 30 MeV
		$2.6 \cdot 10^{10}$ p/cm ² at 60 MeV
NIEL equivalent 10 MeV proton fluence	1 mm	$3.6 \cdot 10^{11}$ p/cm ²
	2 mm	$1.8 \cdot 10^{11}$ p/cm ²
SEU LET threshold	-	25 MeV cm ² / mg
SEL LET threshold	-	60 MeV cm ² / mg

* New values for PHI: TID(Si) < 30 krad with 1 mm Al